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## appendix

# A

## Bragg's Diffraction Law and X-ray Diffraction

### Bragg's Diffraction Condition

X-rays are electromagnetic (EM) waves with wavelengths typically in the range from 0.01 nm to a few nanometers. This wavelength region is comparable with typical interplanar spacings in crystals. When an X-ray beam impinges on a crystal, the waves in the beam interact with the planes of atoms in the crystal and, as a result, the waves become scattered and the X-ray beam becomes diffracted. An analogy with radio waves may help. Radio waves with wavelengths in the range 1–10 m (short waves and VHF waves) easily interact with objects of comparable size. It is well known that these radio waves become scattered by objects of comparable size such as trees, houses, and buildings. However, long-wave radio waves with wavelengths in kilometers do not become scattered by these objects because the object sizes now are much smaller than the wavelength.

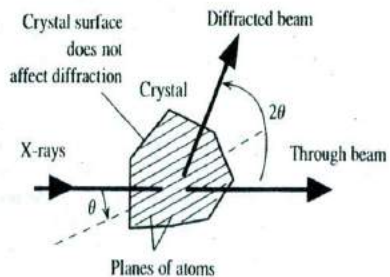
When X-rays strike a crystal, the EM waves penetrate the crystal structure. Each plane of atoms in the crystal reflects a portion of the waves. The reflected waves from different planes then interfere with each other and give rise to a **diffracted beam** which is at a well-defined angle  $\theta$  to the incident beam as depicted in Figure A.1. Some of the incident beam goes through the crystal undiffracted and some of the beam becomes diffracted. Further, the diffracted rays exist only in certain directions. These diffraction directions correspond to well-defined diffraction angles  $2\theta$ , as defined in Figure A.1. The diffraction angle  $2\theta$ , the wavelength of the X-rays  $\lambda$ , and the interplanar separation  $d$  of the diffraction planes within the crystal are related through the **Bragg diffraction condition**, that is,

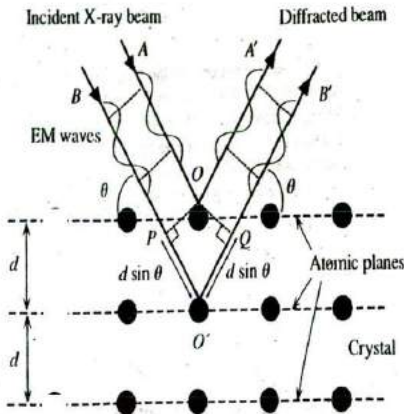
*Bragg's law*

$$2d \sin \theta = n\lambda \quad n = 1, 2, 3, \dots$$

[A.1]

**Figure A.1** A schematic illustration of X-ray diffraction by a crystal. X-rays penetrate the crystal and then become diffracted by a series of atomic planes.





**Figure A.2** Diffraction involves X-ray waves being reflected by various atomic planes in the crystal. These waves interfere constructively to form a diffracted beam only for certain diffraction angles that satisfy the Bragg condition.

Consider X-rays penetrating a crystal structure and becoming reflected by a given set of atomic planes as shown in Figure A.2. We can consider an X-ray beam to be many parallel waves that are in phase. These waves penetrate the crystal structure and become reflected at successive atomic planes. The interplanar separation of these planes is  $d$ . Waves reflected from adjacent atomic planes interfere constructively to constitute a diffracted beam only when the path difference between the rays is an integer multiple of the wavelength—a requirement of *constructive interference*. This will only be the case for certain directions of reflection. For simplicity, we will consider two waves  $A$  and  $B$  in an X-ray beam being reflected from two consecutive atomic planes in the crystal. The angle between the X-rays and the atomic planes is  $\theta$  as defined in Figure A.2. Initially the waves  $A$  and  $B$  are in phase. Wave  $A$  is reflected from the first plane, whereas wave  $B$  is reflected from the second plane. When wave  $A$  is reflected at  $O$ , wave  $B$  is at  $P$ . Wave  $B$  becomes reflected from  $O'$  on the second plane and then moves along reflected  $B'$ . Wave  $A$  has to travel a further distance,  $PO'Q$ , equivalent to  $2d \sin \theta$  before reaching wave  $A$ . The path difference between the two reflected waves  $A'$  and  $B'$  is  $PO'Q$  or  $2d \sin \theta$ . For constructive interference this must be  $n\lambda$  where  $n$  is an integer. Otherwise the reflected waves will interfere destructively and cancel each other out. Thus the condition for the existence of a diffracted beam is that the path difference between  $A'$  and  $B'$  should be a multiple of the wavelength  $\lambda$ ; which is Equation A.1. The diffraction condition in Equation A.1 is referred to as **Bragg's law**. The angle  $\theta$  is called the **Bragg angle**, whereas  $2\theta$  is called the **diffraction angle**. The index  $n$  is called the **order of diffraction**. The incidence angle  $\theta$  is the angle between the incident X-ray and the atomic planes within the crystal and not the angle at the actual crystal surface. The crystal surface, whatever shape, does not affect the diffraction process because X-rays penetrate the crystal and then become diffracted by a series of parallel atomic planes. The Bragg diffraction condition has much wider applications than just crystallography; for example, it is of central importance to the operation of modern semiconductor lasers.

## X-ray Diffraction and Study of Crystal Structures

When an X-ray beam is incident on a single crystal, the scattered beam from a given set of planes in the crystal is at an angle  $2\theta$  that satisfies the Bragg law. In three dimensions, all directions from the crystal that are at an angle  $2\theta$  to the incident beam define a cone as shown in Figure A.3a

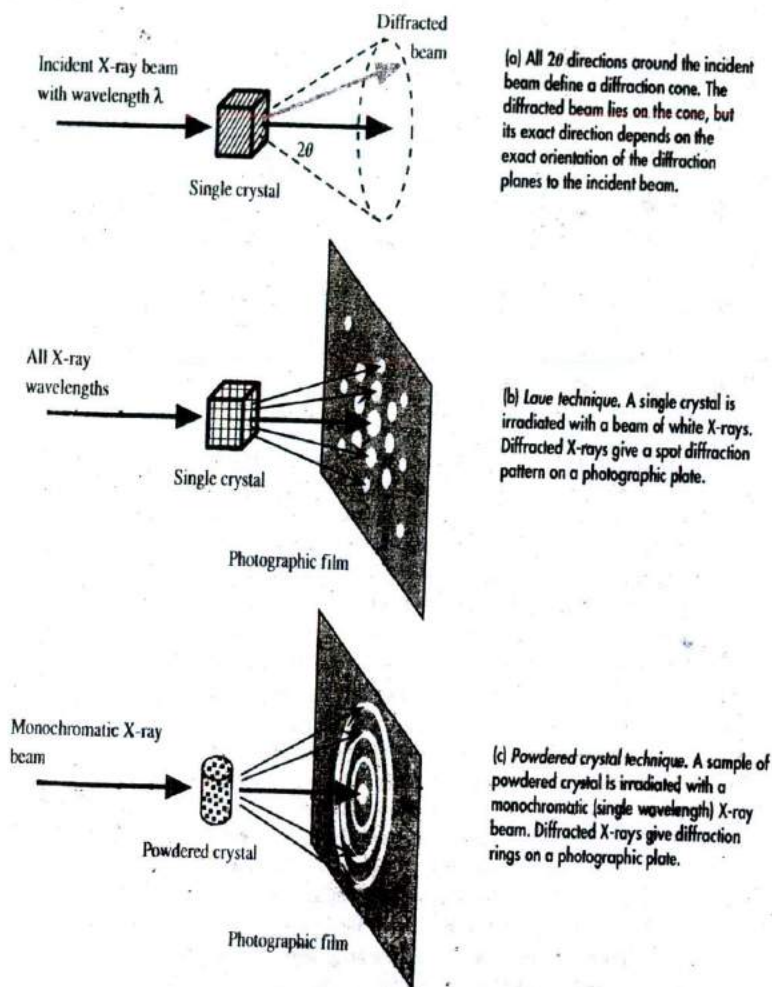


Figure A.3

with its apex at the crystal. This is called a *diffraction cone*. There are many such diffraction cones, each corresponding to a different set of diffraction planes with a distinct set of Miller indices ( $hkl$ ). Although all lines lying on a diffraction cone satisfy the Bragg condition, the exact direction of the diffracted beam depends on the exact orientation (or tilt) of the diffracting planes to the incident ray. When a monochromatic X-ray beam is incident on a single crystal, as illustrated in Figure A.3a, the diffracted beam is along one particular direction on the diffraction cone for that set of diffraction planes ( $hkl$ ) with a particular orientation to the incident beam.

The *Lave technique* of studying crystal structures involves irradiating a single crystal with a white X-ray beam that has a wide range of wavelengths. A photographic plate is used to capture



the diffraction pattern as shown in Figure A.3b. Effectively we are scanning the wavelength  $\lambda$  and picking up diffractions from various  $(hkl)$  planes each time the Bragg condition is satisfied. Thus, whenever  $\lambda$  and  $d$  for a particular set of  $(hkl)$  planes satisfy the Bragg condition, there is a diffraction. The diffraction pattern is a spot pattern where each spot is the result of diffraction from a given set of  $(hkl)$  planes oriented in a particular way to the incident beam. By using a range of wavelengths we ensure that the required wavelength is available for obtaining diffraction for a given set of planes. The relative positions of the spots are used to determine the crystal structure.

One of the simplest methods for studying crystal structures is the **powder technique** which involves irradiating a powdered crystal, or a polycrystalline sample, with a collimated X-ray beam of known wavelength (monochromatic) as shown in Figure A.3c. Powdering the crystal enables a given set of  $(hkl)$  planes to receive the X-rays at many different angles  $\theta$  and at many different orientations, or tilts. Put differently, it allows the angle  $\theta$  to be scanned for differently oriented crystals. Since all possible crystal orientations are present by virtue of powdering, the diffracted rays form diffraction cones and the diffraction pattern developed on a photographic plate has *diffraction rings* as shown in Figure A.3c.

Each diffraction ring in the powder technique in Figure A.3c represents diffraction from a given set of  $(hkl)$  planes. Whenever the angle  $\theta$  satisfies the Bragg law for a given set of atomic planes, with Miller indices  $(hkl)$  and with an interplanar separation  $d_{hkl}$ , there is a diffracted beam. An X-ray detector placed at an angle  $2\theta$  with respect to the through-beam will register a peak in the detected X-ray intensity, as shown in Figure A.4a. The instrument that allows this type of X-ray diffraction study is called a **diffractometer**. The variation of the detected intensity with the diffraction angle  $2\theta$  represents the diffraction pattern of the crystal. The particular diffraction pattern depicted in Figure A.4b is for aluminum, an FCC crystal. Different crystals exhibit different diffraction patterns.

In the case of cubic crystals, the interplanar spacing  $d$  is related to the Miller indices of a plane  $(hkl)$ . The separation  $d_{hkl}$  between adjacent  $(hkl)$  planes is given by

$$d_{hkl} = \frac{a}{\sqrt{h^2 + k^2 + l^2}} \quad \text{[A.2]}$$

*Interplanar separation in cubic crystals*

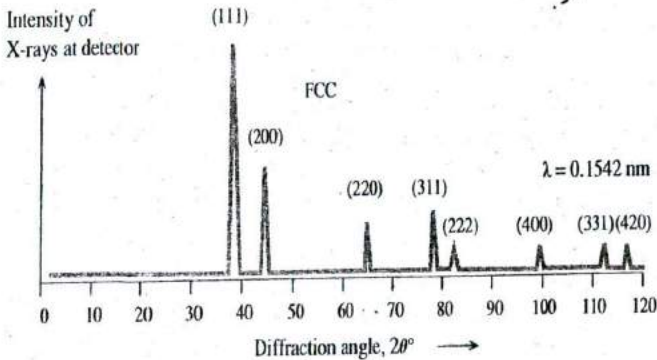
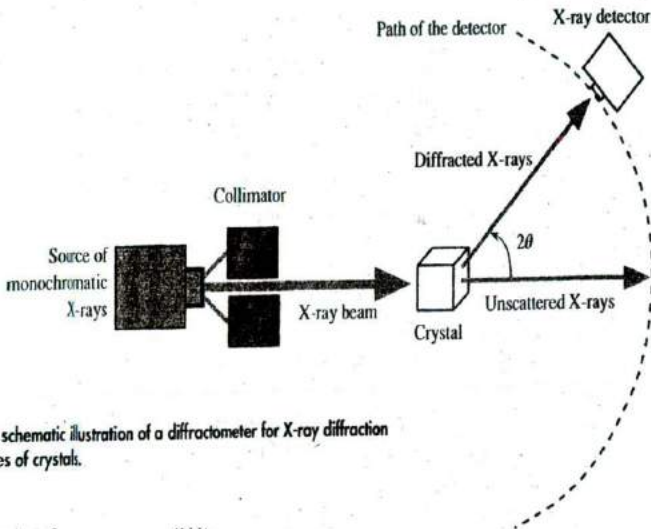
where  $a$  is the lattice parameter (side of the cubic unit cell). When we substitute for  $d = d_{hkl}$  in the Bragg condition in Equation A.1, square both sides, and rearrange the equation, we find

$$(\sin \theta)^2 = \frac{n^2 \lambda^2}{4a^2} (h^2 + k^2 + l^2) \quad \text{[A.3]}$$

*Bragg condition for cubic crystals*

This is essentially **Bragg's law for cubic crystals**. The diffraction angle increases with  $(h^2 + k^2 + l^2)$ . Higher-order Miller indices, those with greater values of  $(h^2 + k^2 + l^2)$ , give rise to wider diffraction angles. For example, the diffraction angle for (111) is smaller than that for (200) because  $(h^2 + k^2 + l^2)$  is 3 for (111) and 4 for (200). Furthermore, with  $\lambda$  and  $a$  values that are typically involved in X-ray diffraction, second- and higher-order diffraction peaks,  $n = 2, 3, \dots$ , can be ruled out.

In the case of the simple cubic crystal all possible  $(hkl)$  planes give rise to diffraction peaks with diffraction angles satisfying the Bragg law or Equation A.3. The latter equation therefore defines a diffraction pattern for the simple cubic crystal structure because it generates all the possible values of  $2\theta$  for all the planes in the cubic crystal. In the case of FCC and BCC crystals, however, not all  $(hkl)$  planes give rise to diffraction peaks predicted by Equation A.3. Examination



**Figure A.4** A schematic diagram of a diffractometer and the diffraction pattern obtained from an FCC crystal.

of the diffraction pattern in Figure A.4b for an FCC crystal shows that only those planes with Miller indices that are either all odd or all even integers give rise to diffraction peaks. There are no diffractions from those planes with mixed odd and even integers.

The Bragg law for the cubic crystals in Equation A.3 is a necessary diffraction condition but not sufficient because diffraction involves the interaction of EM waves with the electrons in the crystal. To determine whether there will be a diffraction peak from a set of planes in a crystal we also have to consider the distributions of the atoms and their electrons in the crystal. In FCC and BCC structures diffractions from certain planes are missing because the atoms on these planes give rise to out-of-phase reflections.

## appendix

# B

## Flux, Luminous Flux, and the Brightness of Radiation

Many optoelectronic light emitting devices are compared by their luminous efficiencies, which requires a knowledge of photometry. **Radiometry** is the science of radiation measurement, for example, the measurement of emitted, absorbed, reflected, transmitted radiation energy; radiation is understood to mean electromagnetic energy in the optical frequency range (ultraviolet, visible, and infrared). **Photometry**, on the other hand, is a subset of radiometry in which radiation is measured with respect to the spectral responsivity of the eye, that is, over the visible spectrum and by taking into account the spectral visual sensitivity of the eye under normal light adapted conditions, i.e., photopic conditions.

**Flux** ( $\Phi$ ) in radiometry has three related definitions, **radiant**, **luminous** and **photon flux**, which correspond to the rate of flow of radiation energy, perceptible visual energy, and photons, respectively. (Notice that, in radiometry, these fluxes are not defined in terms of flow per unit area.) For example, **radiant flux** is the energy flow per unit time in the units of Watts. Radiometric quantities, such as **radiant flux**  $\Phi_e$ , radiant energy flow per unit time, usually have a subscript  $e$  and invariably involve energy or power. Radiometric **spectral** quantities, such as **spectral radiant flux**  $\Phi_{\lambda}$ , refer to the radiometric quantity per unit wavelength; i.e.,  $\Phi_{\lambda} = d\Phi_e/d\lambda$  is the radiant flux per unit wavelength.

**Luminous flux** or **photometric flux**  $\Phi_v$ , is the visual "brightness" of a source as observed by an average daylight adapted eye and is proportional to the radiant flux (radiation power emitted) of the source and the efficiency of the eye to detect the spectrum of the emitted radiation. While the eye can see a red color source, it cannot see an infrared source, and the luminous flux of the infrared source would be zero. Similarly, the eye is less efficient in the violet than in the green region, and less radiant flux is needed to have a green source at the same luminous flux as the blue source. Luminous flux  $\Phi_v$  is measured in **lumens** (lm), and at a particular wavelength it is given by

$$\Phi_v = \Phi_e \times K \times \eta_{eye}$$

Luminous  
flux in lumens

where  $\Phi_e$  is the radiant flux (in Watts),  $K$  is a conversion constant (standardized to be 633 lm/W).  $\eta_{eye}$  (also denoted as  $V$ ) is the **luminous efficiency** (**luminous efficacy**) of the daylight adapted eye, which is unity at 555 nm;  $\eta_{eye}$  depends on the wavelength. By definition, a 1 W light source emitting at 555 nm (green, where  $\eta_{eye} = 1$ ) emits a luminous flux of 633 lm. The same 1 W light source at 650 nm (red), where  $\eta_{eye} = 0.11$ , emits only 70 lm. When we buy a light bulb, we are essentially paying for lumens because it is luminous flux that the eye perceives. A typical 60 W incandescent lamp provides roughly 900 lm. Fluorescent tubes provide more luminous flux



output than incandescent lamps for the same electric power input as they have more spectral emission in the visible region and make better use of the eye's spectral sensitivity. Some examples are 100 W incandescent lamps, 1300–1800 lm, depending on the filament operating temperature (hence bulb design), and 25 W compact fluorescent lamps, 1500–1750 lm.

**Luminous efficacy of a light source** (such as a lamp) in the lighting industry is the efficiency with which an electric light source converts the input electric power (W) into an emitted luminous flux (lm). A 100 W light bulb producing 1700 lm has an efficacy of 17 lm/W. While at present the LED efficacies are below those of fluorescent tubes, rapid advances in LED technologies are bringing the expected efficacies to around 50 lm/W or higher. LEDs as solid-state lamps have much longer lifetimes and much higher reliability, and hence are expected to be more economical than incandescent and fluorescent lamps.



From left to right Michael Faraday, Thomas Henry Huxley, Charles Wheatstone, David Brewster and John Tyndall. Professor Tyndall has been attributed with the first demonstration (1854) of light being guided along a water jet, which is based in total internal reflection.

1 SOURCE: Courtesy of AIP Emilio Segrè Visual Archives, Zeleny Collection.

$d$ (subscript)	donor, e.g., $N_d$ = donor concentration ( $\text{m}^{-3}$ )
dc	direct current
$d_{ij}$	piezoelectric coefficients
$E$	energy; electric field ( $\text{V m}^{-1}$ ) (Ch. 9)
$E_a, E_d$	acceptor and donor energy levels
$E_c, E_v$	conduction band edge, valence band edge
$E_{\text{ex}}$	exchange interaction energy
$E_f, E_{FO}$	Fermi energy, Fermi energy at 0 K
$E_g$	bandgap energy
$E_{\text{mag}}$	magnetic energy
$\mathcal{E}$	electric field ( $\text{V m}^{-1}$ )
$\mathcal{E}_{\text{br}}$	dielectric strength or breakdown field ( $\text{V m}^{-1}$ )
$\mathcal{E}_{\text{loc}}$	local electric field
$e$	electronic charge ( $1.602 \times 10^{-19}$ C)
$e$ (subscript)	electron, e.g., $\mu_e$ = electron drift mobility; electronic
eff (subscript)	effective, e.g., $\mu_{\text{eff}}$ = effective drift mobility
EHP	electron-hole pair
EM	electromagnetic
EMF (emf)	electromagnetic force (V)
$F$	force (N); function
$f$	frequency; function
$f(E)$	Fermi-Dirac function
FCC	face-centered cubic
FET	field effect transistor
$G$	rate of generation
$G_{\text{ph}}$	rate of photogeneration
$G_p$	parallel conductance ( $\Omega^{-1}$ )
$g(E)$	density of states
$g$	conductance; transconductance (A/V); piezoelectric voltage coefficient (Ch. 7)
$g_d$	incremental or dynamic conductance (A/V)
$g_m$	mutual transconductance (A/V)
$H, H$	magnetic field intensity (strength), magnetizing field ( $\text{A m}^{-1}$ )
$h$	Planck's constant ( $6.6261 \times 10^{-34}$ J s)
$\hbar$	Planck's constant divided by $2\pi$ ( $\hbar = 1.0546 \times 10^{-34}$ J s)
$h$ (subscript)	hole, e.g., $\mu_h$ = hole drift mobility
$h_{FE}, h_{fe}$	dc current gain, small-signal (ac) current gain in the common emitter configuration
HCP	hexagonal close-packed
HF	high frequency
$I$	electric current (A); moment of inertia ( $\text{kg m}^2$ ) (Ch. 1)
$I$	light intensity ( $\text{W m}^{-2}$ )
$I, i$ (subscript)	quantity related to ionic polarization
$I_{\text{br}}$	breakdown current
$I_B, I_C, I_E$	base, collector, and emitter currents in a BJT



## appendix

# C

## Major Symbols and Abbreviations

<i>A</i>	area; cross-sectional area; amplification
<i>a</i>	lattice parameter; acceleration; amplitude of vibrations; half-channel thickness in a JFET (Ch. 6)
<i>a</i> (subscript)	acceptor, e.g., $N_a$ = acceptor concentration ( $\text{m}^{-3}$ )
ac	alternating current
$a_0$	Bohr radius (0.0529 nm)
$A_V, A_P$	voltage amplification, power amplification
APF	atomic packing factor
<b>B, <i>B</i></b>	magnetic field vector (T), magnetic field
<i>B</i>	frequency bandwidth
$B_c$	critical magnetic field
$B_m$	maximum magnetic field
$B_0, B_e$	Richardson–Dushman constant, effective Richardson–Dushman constant
BC	base collector
BCC	body-centered cubic
BE	base emitter
BJT	bipolar junction transistor
<i>C</i>	capacitance; composition; the Nordheim coefficient ( $\Omega \text{ m}$ )
<i>c</i>	speed of light ( $3 \times 10^8 \text{ m s}^{-1}$ ); specific heat capacity ( $\text{J K}^{-1} \text{ kg}^{-1}$ )
$C_{dep}$	depletion layer capacitance
$C_m$	molar heat capacity ( $\text{J K}^{-1} \text{ mol}^{-1}$ )
$C_{diff}$	diffusion (storage) capacitance of a forward-biased <i>pn</i> junction
$c_s$	specific heat capacity ( $\text{J K}^{-1} \text{ kg}^{-1}$ )
$C_v$	heat capacity per unit volume ( $\text{J K}^{-1} \text{ m}^{-3}$ )
CB	conduction band; common base
CE	common emitter
CMOS	complementary MOS
CN	coordination number
CVD	chemical vapor deposition
<i>D</i>	diffusion coefficient ( $\text{m}^2 \text{ s}^{-1}$ ); thickness; electric displacement ( $\text{C m}^{-2}$ )
<i>d</i>	density ( $\text{kg m}^{-3}$ ); distance; separation of the atomic planes in a crystal, separation of capacitor plates; piezoelectric coefficient; mean grain size (Ch. 2)

$i$	instantaneous current (A); small-signal (ac) current, $i = \delta I$
$i$ (subscript)	intrinsic, e.g., $n_i$ = intrinsic concentration
$i_b, i_c, i_e$	small signal base, collector, and emitter currents ( $\delta I_B, \delta I_C, \delta I_E$ ) in a BJT
IC	integrated circuit
$J$	current density ( $A\ m^{-2}$ )
$\mathbf{J}$	total angular momentum vector
$j$	imaginary constant: $\sqrt{-1}$
$J_c$	critical current density ( $A\ m^{-2}$ )
$J_p$	pyroelectric current density
JFET	junction FET
$K$	spring constant (Ch. 1); phonon wavevector ( $m^{-1}$ ); bulk modulus (Pa); dielectric constant (Ch. 7)
$k$	Boltzmann constant ( $k = R/N_A = 1.3807 \times 10^{-23}\ J\ K^{-1}$ ); wavenumber ( $k = 2\pi/\lambda$ ), wavevector ( $m^{-1}$ ); electromechanical coupling factor (Ch. 7)
KE	kinetic energy
$L$	total orbital angular momentum
$L$	length; inductance
$\ell$	length; mean free path; orbital angular momentum quantum number
$L_{ch}$	channel length in a FET
$L_e, L_h$	electron and hole diffusion lengths
$\ell_n, \ell_p$	lengths of the $n$ - and $p$ -regions outside depletion region in a $pn$ junction
$\ln(x)$	natural logarithm of $x$
LCAO	linear combination of atomic orbitals
$\mathbf{M}, M$	magnetization vector ( $A\ m^{-1}$ ), magnetization ( $A\ m^{-1}$ )
$M$	multiplication in avalanche effect
$M_{at}$	relative atomic mass; atomic mass; "atomic weight" ( $g\ mol^{-1}$ )
$M_r$	remnant or residual magnetization ( $A\ m^{-1}$ ); reduced mass of two bodies $A$ and $B$ , $M_r = M_A M_B / (M_A + M_B)$
$M_{sat}$	saturation magnetization ( $A\ m^{-1}$ )
$m$	mass (kg)
$m_e$	mass of the electron in free space ( $9.10939 \times 10^{-31}\ kg$ )
$m_e^*$	effective mass of the electron in a crystal
$m_h^*$	effective mass of a hole in a crystal
$m_l$	magnetic quantum number
$m_s$	spin magnetic quantum number
MO $\dot{S}$ (MOST)	metal-oxide-semiconductor (transistor)
MOSFET	metal-oxide-semiconductor FET
$N$	number of atoms or molecules; number of atoms per unit volume ( $m^{-3}$ ) (Chs. 7 and 9); number of turns on a coil (Ch. 8)
$N_A$	Avogadro's number ( $6.022 \times 10^{23}\ mol^{-1}$ )
$n$	electron concentration (number per unit volume); atomic concentration; principal quantum number; integer number; refractive index (Ch. 9)
$n^+$	heavily doped $n$ -region
$n_{at}$	number of atoms per unit volume

$N_c, N_v$	effective density of states at the conduction and valence band edges ( $m^{-3}$ )
$N_d, N_d^+$	donor and ionized donor concentrations ( $m^{-3}$ )
$n_e, n_o$	refractive index for extraordinary and ordinary waves in a birefringent crystal
$n_i$	intrinsic concentration ( $m^{-3}$ )
$n_{no}, p_{po}$	equilibrium majority carrier concentrations ( $m^{-3}$ )
$n_{po}, p_{no}$	equilibrium minority carrier concentrations ( $m^{-3}$ )
$N_s$	concentration of electron scattering centers
$n_v$	velocity density function; vacancy concentration ( $m^{-3}$ )
$P$	probability; pressure (Pa); power (W) or power loss (W)
$\mathbf{p}, \mathbf{p}$	electric dipole moment (C m)
$p$	hole concentration ( $m^{-3}$ ); momentum ( $kg\ m\ s^{-1}$ ); pyroelectric coefficient ( $C\ m^{-2}\ K^{-1}$ ) (Ch. 7)
$p^+$	heavily doped $p$ -region
$p_{av}$	average dipole moment per molecule
$p_e$	electron momentum ( $kg\ m\ s^{-1}$ )
$PE$	potential energy
$p_{induced}$	induced dipole moment (C m)
$p_o$	permanent dipole moment (C m)
PET	polyester, polyethylene terephthalate
PZT	lead zirconate titanate
$Q$	charge (C); heat (J); quality factor
$Q'$	rate of heat flow (W)
$q$	charge (C); an integer number used in lattice vibrations (Ch. 4)
$R$	gas constant ( $N_A k = 8.3145\ J\ mol^{-1}\ K^{-1}$ ); resistance; radius; reflection coefficient (Ch. 3); rate of recombination (Ch. 5)
$R$	reflectance (Ch. 9)
$\mathcal{R}_x, \mathcal{R}_y$	pyroelectric current and voltage responsivities
$\mathbf{r}$	position vector
$r$	radial distance; radius; interatomic separation; resistance per unit length
$r$	reflection coefficient (Ch. 9)
$R_H$	Hall coefficient ( $m^3\ C^{-1}$ )
$r_o$	bond length, equilibrium separation
rms	root mean square
$S$	total spin momentum, intrinsic angular momentum; Poynting vector (Ch. 9)
$S$	cross-sectional area of a scattering center; Seebeck coefficient, thermoelectric power ( $V\ m^{-1}$ ); strain (Ch. 7)
$S_{band}$	number of states per unit volume in the band
$S_j$	strain along direction $j$
SCL	space charge layer
$T$	temperature in Kelvin; transmission coefficient
$T$	transmittance
$t$	time (s); thickness (m)
$t$	transmission coefficient
$\tan \delta$	loss tangent



$T_C$	Curie temperature
$T_c$	critical temperature (K)
$T_j$	mechanical stress along direction $j$ (Pa)
TC	thermocouple
TCC	temperature coefficient of capacitance ( $K^{-1}$ )
TCR	temperature coefficient of resistivity ( $K^{-1}$ )
$U$	total internal energy
$u$	mean speed (of electron) ( $m\ s^{-1}$ )
$V$	voltage; volume; $PE$ function of the electron, $PE(x)$
$V_{br}$	breakdown voltage
$V_o$	built-in voltage
$V_p$	pinch-off voltage
$V_r$	reverse bias voltage
$v, V$	velocity ( $m\ s^{-1}$ ); instantaneous voltage (V)
$\frac{v}{v^2}$	mean square velocity; mean square voltage
$v_{dx}$	drift velocity in the $x$ direction
$v_e, v_{rms}$	effective velocity or rms velocity of the electron
$v_F$	Fermi speed
$v_g, v_g$	group velocity
$v_{th}$	thermal velocity
VB	valence band
$W$	width; width of depletion layer with applied voltage; dielectric loss
$W_o$	width of depletion region with no applied voltage
$W_n, W_p$	width of depletion region on the $n$ -side and on the $p$ -side with no applied voltage
$X$	atomic fraction
$Y$	admittance ( $\Omega^{-1}$ ); Young's modulus (Pa)
$Z$	impedance ( $\Omega$ ); atomic number, number of electrons in the atom
$\alpha$	polarizability; temperature coefficient of resistivity ( $K^{-1}$ ); absorption coefficient ( $m^{-1}$ ); gain or current transfer ratio from emitter to collector of a BJT
$\beta$	current gain $I_C/I_B$ of a BJT; Bohr magneton ( $9.2740 \times 10^{-24}\ J\ T^{-1}$ ); spring constant (Ch. 4)
$\beta_S$	Schottky coefficient
$\gamma$	emitter injection efficiency (Ch. 6); gyromagnetic ratio (Ch. 8); Grüneisen parameter (Ch. 4); loss coefficient in the Lorentz oscillator model
$\Gamma, \Gamma_{ph}$	flux ( $m^{-2}\ s^{-1}$ ), photon flux (photons $m^{-2}\ s^{-1}$ )
$\delta$	small change; skin depth (Ch. 2); loss angle (Ch. 7); domain wall thickness (Ch. 8); penetration depth (Ch. 9)
$\Delta$	change, excess (e.g., $\Delta n =$ excess electron concentration)
$\nabla^2$	$\partial^2/\partial x^2 + \partial^2/\partial y^2 + \partial^2/\partial z^2$
$\epsilon$	$\epsilon_o\epsilon_r$ , permittivity of a medium ( $C\ V^{-1}\ m^{-1}$ or $F\ m^{-1}$ ); elastic strain
$\epsilon_o$	permittivity of free space or absolute permittivity ( $8.8542 \times 10^{-12}\ C\ V^{-1}\ m^{-1}$ or $F\ m^{-1}$ )

$\epsilon_r$	relative permittivity or dielectric constant
$\eta$	efficiency; quantum efficiency; ideality factor
$\theta$	angle; an angular spherical coordinate; thermal resistance; angle between a light ray and normal to a surface (Ch. 9)
$\kappa$	thermal conductivity ( $\text{W m}^{-1} \text{K}^{-1}$ ); dielectric constant
$\lambda$	wavelength (m); thermal coefficient of linear expansion ( $\text{K}^{-1}$ ); electron mean free path in the bulk crystal (Ch. 2); characteristic length (Ch. 8)
$\mu, \mu$	magnetic dipole moment ( $\text{A m}^2$ ) (Ch. 3)
$\mu$	$\mu_0\mu_r$ , magnetic permeability ( $\text{H m}^{-1}$ ); chemical potential (Ch. 5)
$\mu_0$	absolute permeability ( $4\pi \times 10^{-7} \text{H m}^{-1}$ )
$\mu_r$	relative permeability
$\mu_m, \mu_n$	magnetic dipole moment ( $\text{A m}^2$ ) (Ch. 8)
$\mu_d$	drift mobility ( $\text{m}^2 \text{V}^{-1} \text{s}^{-1}$ )
$\mu_h, \mu_e$	hole drift mobility, electron drift mobility ( $\text{m}^2 \text{V}^{-1} \text{s}^{-1}$ )
$\nu$	frequency (Hz); Poisson's ratio; volume fraction (Ch. 7)
$\pi$	pi, 3.14159...; piezoresistive coefficient ( $\text{Pa}^{-1}$ )
$\pi_L, \pi_T$	longitudinal and transverse piezoresistive coefficients ( $\text{Pa}^{-1}$ )
$\Pi$	Peltier coefficient (V)
$\rho$	resistivity ( $\Omega \text{m}$ ); density ( $\text{kg m}^{-3}$ ); charge density ( $\text{C m}^{-3}$ )
$\rho_E$	energy density ( $\text{J m}^{-3}$ )
$\rho_{\text{net}}$	net space charge density ( $\text{C m}^{-3}$ )
$\rho J^2$	Joule heating per unit volume ( $\text{W m}^{-3}$ )
$\sigma$	electrical conductivity ( $\Omega^{-1} \text{m}^{-1}$ ); surface concentration of charge ( $\text{C m}^{-2}$ ) (Ch. 7)
$\sigma_P$	polarization charge density ( $\text{C m}^{-2}$ )
$\sigma_n$	free surface charge density ( $\text{C m}^{-2}$ )
$\sigma_S$	Stefan's constant ( $5.670 \times 10^{-8} \text{W m}^{-2} \text{K}^{-4}$ )
$\tau$	time constant; mean electron scattering time; relaxation time; torque (N m)
$\tau_g$	mean time to generate an electron-hole pair
$\phi$	angle; an angular spherical coordinate
$\Phi$	work function (J or eV), magnetic flux (Wb)
$\Phi_e$	radiant flux (W)
$\Phi_m$	metal work function (J or eV)
$\Phi_n$	energy required to remove an electron from an <i>n</i> -type semiconductor (J or eV)
$\Phi_v$	luminous flux (lumens)
$\chi$	volume fraction; electron affinity; susceptibility ( $\chi_e$ is electrical; $\chi_m$ is magnetic)
$\Psi(x, t)$	total wavefunction
$\psi(x)$	spatial dependence of the electron wavefunction under steady-state conditions
$\psi_k(x)$	Bloch wavefunction, electron wavefunction in a crystal
$\psi_{\text{hyb}}$	hybrid orbital
$\omega$	angular frequency ( $2\pi\nu$ ); oscillation frequency ( $\text{rad s}^{-1}$ )
$\omega_I$	ionic polarization resonance frequency (angular)
$\omega_n$	resonance or natural frequency (angular) of an oscillating system.

Element	Symbol	Z	Atomic Mass (g mol <sup>-1</sup> )	Electronic Structure	Density (g cm <sup>-3</sup> ) (*at 0 °C, 1 atm)	Crystal in Solid State
Arsenic	As	33	74.92	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>3</sup>	5.72	Rhombohedral
Selenium	Se	34	78.96	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>4</sup>	4.80	Hexagonal
Bromine	Br	35	79.90	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>5</sup>	3.12	Orthorhombic
Krypton	Kr	36	83.80	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>6</sup>	3.74	FCC
Rubidium	Rb	37	85.47	[Kr]5s <sup>1</sup>	1.53	BCC
Strontium	Sr	38	87.62	[Kr]5s <sup>2</sup>	2.6	FCC
Yttrium	Y	39	88.90	[Kr]4d <sup>1</sup> 5s <sup>2</sup>	4.5	HCP
Zirconium	Zr	40	91.22	[Kr]4d <sup>2</sup> 5s <sup>2</sup>	6.50	HCP
Niobium	Nb	41	92.91	[Kr]4d <sup>4</sup> 5s <sup>1</sup>	8.55	BCC
Molybdenum	Mo	42	95.94	[Kr]4d <sup>5</sup> 5s <sup>1</sup>	10.2	BCC
Technetium	Tc	43	(97.91)	[Kr]4d <sup>5</sup> 5s <sup>2</sup>	11.5	HCP
Ruthenium	Ru	44	101.07	[Kr]4d <sup>7</sup> 5s <sup>1</sup>	12.2	HCP
Rhodium	Rh	45	102.91	[Kr]4d <sup>8</sup> 5s <sup>1</sup>	12.4	FCC
Palladium	Pd	46	106.42	[Kr]4d <sup>10</sup>	12.0	FCC
Silver	Ag	47	107.87	[Kr]4d <sup>10</sup> 5s <sup>1</sup>	10.5	FCC
Cadmium	Cd	48	112.41	[Kr]4d <sup>10</sup> 5s <sup>2</sup>	8.65	HCP
Indium	In	49	114.82	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>1</sup>	7.31	FCT
Tin	Sn	50	118.71	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>2</sup>	7.30	BCT
Antimony	Sb	51	121.75	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>3</sup>	6.68	Rhombohedral
Tellurium	Te	52	127.60	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>4</sup>	6.24	Hexagonal
Iodine	I	53	126.91	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>5</sup>	4.92	Orthorhombic
Xenon	Xe	54	131.29	[Kr]4d <sup>10</sup> 5s <sup>2</sup> p <sup>6</sup>	0.0059*	FCC
Cesium	Cs	55	132.90	[Xe]6s <sup>1</sup>	1.87	BCC
Barium	Ba	56	137.33	[Xe]6s <sup>2</sup>	3.62	BCC
Lanthanum	La	57	138.91	[Xe]5d <sup>1</sup> 6s <sup>2</sup>	6.15	HCP
Cerium	Ce	58	140.12	[Xe]4f <sup>1</sup> 5d <sup>1</sup> 6s <sup>2</sup>	6.77	FCC
Praseodymium	Pr	59	140.91	[Xe]4f <sup>3</sup> 6s <sup>2</sup>	6.77	HCP
Neodymium	Nd	60	144.24	[Xe]4f <sup>4</sup> 6s <sup>2</sup>	7.00	HCP
Promethium	Pm	61	(145)	[Xe]4f <sup>5</sup> 6s <sup>2</sup>	7.26	Hexagonal
Samarium	Sm	62	150.4	[Xe]4f <sup>6</sup> 6s <sup>2</sup>	7.5	Rhombohedral
Europium	Eu	63	151.97	[Xe]4f <sup>7</sup> 6s <sup>2</sup>	5.24	BCC
Gadolinium	Gd	64	157.25	[Xe]4f <sup>7</sup> 5d <sup>1</sup> 6s <sup>2</sup>	7.90	HCP
Terbium	Tb	65	158.92	[Xe]4f <sup>9</sup> 6s <sup>2</sup>	8.22	HCP
Dysprosium	Dy	66	162.50	[Xe]4f <sup>10</sup> 6s <sup>2</sup>	8.55	HCP
Holmium	Ho	67	164.93	[Xe]4f <sup>11</sup> 6s <sup>2</sup>	8.80	HCP
Erbium	Er	68	167.26	[Xe]4f <sup>12</sup> 6s <sup>2</sup>	9.06	HCP
Thulium	Tm	69	168.93	[Xe]4f <sup>13</sup> 6s <sup>2</sup>	9.32	HCP
Ytterbium	Yb	70	173.04	[Xe]4f <sup>14</sup> 6s <sup>2</sup>	6.90	FCC
Lutetium	Lu	71	174.97	[Xe]4f <sup>14</sup> 5d <sup>1</sup> 6s <sup>2</sup>	9.84	HCP
Hafnium	Hf	72	178.49	[Xe]4f <sup>14</sup> 5d <sup>2</sup> 6s <sup>2</sup>	13.3	HCP
Tantalum	Ta	73	180.95	[Xe]4f <sup>14</sup> 5d <sup>3</sup> 6s <sup>2</sup>	16.4	BCC
Tungsten	W	74	183.84	[Xe]4f <sup>14</sup> 5d <sup>4</sup> 6s <sup>2</sup>	19.3	BCC
Rhenium	Re	75	186.21	[Xe]4f <sup>14</sup> 5d <sup>5</sup> 6s <sup>2</sup>	21.0	HCP



**appendix**

# D

## Elements to Uranium

Element	Symbol	Z	Atomic Mass (g mol <sup>-1</sup> )	Electronic Structure	Density (g cm <sup>-3</sup> ) (*at 0 °C, 1 atm)	Crystal in Solid State
Hydrogen	H	1	1.008	1s <sup>1</sup>	0.00009*	HCP
Helium	He	2	4.003	1s <sup>2</sup>	0.00018*	FCP
Lithium	Li	3	6.941	[He]2s <sup>1</sup>	0.54	BCC
Beryllium	Be	4	9.012	[He]2s <sup>2</sup>	1.85	HCP
Boron	B	5	10.81	[He]2s <sup>2</sup> p <sup>1</sup>	2.5	Rhombohedral
Carbon	C	6	12.01	[He]2s <sup>2</sup> p <sup>2</sup>	2.3	Hexagonal
Nitrogen	N	7	14.007	[He]2s <sup>2</sup> p <sup>3</sup>	0.00125*	HCP
Oxygen	O	8	16.00	[He]2s <sup>2</sup> p <sup>4</sup>	0.00143*	Monoclinic
Fluorine	F	9	18.99	[He]2s <sup>2</sup> p <sup>5</sup>	0.00170*	Monoclinic
Neon	Ne	10	20.18	[He]2s <sup>2</sup> p <sup>6</sup>	0.00090*	FCC
Sodium	Na	11	22.99	[Ne]3s <sup>1</sup>	0.97	BCC
Magnesium	Mg	12	24.31	[Ne]3s <sup>2</sup>	1.74	HCP
Aluminum	Al	13	26.98	[Ne]3s <sup>2</sup> p <sup>1</sup>	2.70	FCC
Silicon	Si	14	28.09	[Ne]3s <sup>2</sup> p <sup>2</sup>	2.33	Diamond
Phosphorus	P	15	30.97	[Ne]3s <sup>2</sup> p <sup>3</sup>	1.82	Triclinic
Sulfur	S	16	32.06	[Ne]3s <sup>2</sup> p <sup>4</sup>	2.0	Orthorhombic
Chlorine	Cl	17	35.45	[Ne]3s <sup>2</sup> p <sup>5</sup>	0.0032*	Orthorhombic
Argon	Ar	18	39.95	[Ne]3s <sup>2</sup> p <sup>6</sup>	0.0018*	FCC
Potassium	K	19	39.09	[Ar]4s <sup>1</sup>	0.86	BCC
Calcium	Ca	20	40.08	[Ar]4s <sup>2</sup>	1.55	FCC
Scandium	Sc	21	44.96	[Ar]3d <sup>1</sup> 4s <sup>2</sup>	3.0	HCP
Titanium	Ti	22	47.87	[Ar]3d <sup>2</sup> 4s <sup>2</sup>	4.5	HCP
Vanadium	V	23	50.94	[Ar]3d <sup>3</sup> 4s <sup>2</sup>	5.8	BCC
Chromium	Cr	24	52.00	[Ar]3d <sup>5</sup> 4s <sup>1</sup>	7.19	BCC
Manganese	Mn	25	54.95	[Ar]3d <sup>5</sup> 4s <sup>2</sup>	7.43	BCC
Iron	Fe	26	55.85	[Ar]3d <sup>6</sup> 4s <sup>2</sup>	7.86	BCC
Cobalt	Co	27	58.93	[Ar]3d <sup>7</sup> 4s <sup>2</sup>	8.90	HCP
Nickel	Ni	28	58.69	[Ar]3d <sup>8</sup> 4s <sup>2</sup>	8.90	FCC
Copper	Cu	29	63.55	[Ar]3d <sup>10</sup> 4s <sup>1</sup>	8.96	FCC
Zinc	Zn	30	65.39	[Ar]3d <sup>10</sup> 4s <sup>2</sup>	7.14	HCP
Gallium	Ga	31	69.72	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>1</sup>	5.91	Orthorhombic
Germanium	Ge	32	72.61	[Ar]3d <sup>10</sup> 4s <sup>2</sup> p <sup>2</sup>	5.32	Diamond

Element	Symbol	Z	Atomic mass (g mol <sup>-1</sup> )	Electronic Structure	Density (g cm <sup>-3</sup> ) (*at 0 °C, 1 atm)	Crystal in Solid State
Osmium	Os	76	190.2	[Xe]4f <sup>14</sup> 5d <sup>6</sup> 6s <sup>2</sup>	22.6	HCP
Iridium	Ir	77	192.22	[Xe]4f <sup>14</sup> 5d <sup>7</sup> 6s <sup>2</sup>	22.5	FCC
Platinum	Pt	78	195.08	[Xe]4f <sup>14</sup> 5d <sup>9</sup> 6s <sup>1</sup>	21.4	FCC
Gold	Au	79	196.97	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>1</sup>	19.3	FCC
Mercury	Hg	80	200.59	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup>	13.55	Rhombohedral
Thallium	Tl	81	204.38	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>1</sup>	11.8	HCP
Lead	Pb	82	207.2	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>2</sup>	11.34	FCC
Bismuth	Bi	83	208.98	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>3</sup>	9.8	Rhombohedral
Polonium	Po	84	(209)	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>4</sup>	9.2	SC
Astatine	At	85	(210)	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>5</sup>	—	—
Radon	Rn	86	(222)	[Xe]4f <sup>14</sup> 5d <sup>10</sup> 6s <sup>2</sup> p <sup>6</sup>	0.0099*	Rhombohedral
Francium	Fr	87	(223)	[Rn]7s <sup>1</sup>	—	—
Radium	Ra	88	226.02	[Rn]7s <sup>2</sup>	5	BCC
Actinium	Ac	89	227.02	[Rn]6d <sup>1</sup> 7s <sup>2</sup>	10.0	FCC
Thorium	Th	90	232.04	[Rn]6d <sup>2</sup> 7s <sup>2</sup>	11.7	FCC
Protactinium	Pa	91	(231.03)	[Rn]5f <sup>2</sup> 6d <sup>1</sup> 7s <sup>2</sup>	15.4	BCT
Uranium	U	92	(238.05)	[Rn]5f <sup>3</sup> 6d <sup>1</sup> 7s <sup>2</sup>	19.07	Orthorhombic



"I don't really start until I get my proofs back from the printers. Then I can begin serious writing."

John Maynard Keynes (1883–1946)

## appendix

# E

## Constants and Useful Information

### Physical Constants

Atomic mass unit	amu	$1.66054 \times 10^{-27} \text{ kg}$
Avogadro's number	$N_A$	$6.02214 \times 10^{23} \text{ mol}^{-1}$
Bohr magneton	$\beta$	$9.2740 \times 10^{-24} \text{ J T}^{-1}$
Boltzmann constant	$k$	$1.3807 \times 10^{-23} \text{ J K}^{-1} = 8.6174 \times 10^{-5} \text{ eV K}^{-1}$
Electron mass in free space	$m_e$	$9.10939 \times 10^{-31} \text{ kg}$
Electron charge	$e$	$1.60218 \times 10^{-19} \text{ C}$
Gas constant	$R$	$8.3145 \text{ J K}^{-1} \text{ mol}^{-1}$ or $\text{m}^3 \text{ Pa K}^{-1} \text{ mol}^{-1}$
Gravitational constant	$G$	$6.6742 \times 10^{-11} \text{ N m}^2 \text{ kg}^{-2}$
Permeability of vacuum or absolute permeability	$\mu_0$	$4\pi \times 10^{-7} \text{ H m}^{-1}$ (or $\text{Wb A}^{-1} \text{ m}^{-1}$ )
Permittivity of vacuum or absolute permittivity	$\epsilon_0$	$8.8542 \times 10^{-12} \text{ F m}^{-1}$
Planck's constant	$h$	$6.626 \times 10^{-34} \text{ J s} = 4.136 \times 10^{-15} \text{ eV s}$
Planck's constant/ $2\pi$	$\hbar$	$1.055 \times 10^{-34} \text{ J s} = 6.582 \times 10^{-16} \text{ eV s}$
Proton rest mass	$m_p$	$1.67262 \times 10^{-27} \text{ kg}$
Rydberg constant	$R_\infty$	$1.0974 \times 10^7 \text{ m}^{-1}$
Speed of light	$c$	$2.9979 \times 10^8 \text{ m s}^{-1}$
Stefan's constant	$\sigma_s$	$5.6704 \times 10^{-8} \text{ W m}^{-2} \text{ K}^{-4}$

### Useful Information

Acceleration due to gravity at $45^\circ$ latitude	$g$	$9.81 \text{ m s}^{-2}$
$kT$ at $T = 293 \text{ K}$ ( $20^\circ \text{C}$ )	$kT$	$0.02525 \text{ eV}$
$kT$ at $T = 300 \text{ K}$ ( $27^\circ \text{C}$ )	$kT$	$0.02585 \text{ eV}$
Bohr radius	$a_0$	$0.0529 \text{ nm}$
1 angstrom	$\text{\AA}$	$10^{-10} \text{ m}$
1 micron	$\mu\text{m}$	$10^{-6} \text{ m}$
1 eV = $1.6022 \times 10^{-19} \text{ J}$		
1 kJ mol $^{-1}$ = $0.010364 \text{ eV atom}^{-1}$		
1 atmosphere (pressure)		
= $1.013 \times 10^5 \text{ Pa}$		



## LED Colors

The table gives the wavelength ranges and colors as usually specified for LEDs.

Color	Blue	Emerald green	Green	Yellow	Amber	Orange	Red orange	Red	Deep red	Infrared
$\lambda$ (nm)	$\lambda < 500$	530-564	565-579	580-587	588-594	595-606	607-615	616-632	633-700	$\lambda > 700$

## Visible Spectrum

The table gives the typical wavelength ranges and color perception by an average person.

Color	Violet	Blue	Green	Yellow	Orange	Red
$\lambda$ (nm)	390-455	455-492	492-577	577-597	597-622	622-780

## Complex Numbers

$$j = (-1)^{1/2} \quad j^2 = -1$$

$$\exp(j\theta) = \cos \theta + j \sin \theta$$

$$Z = a + jb = re^{j\theta}$$

$$r = (a^2 + b^2)^{1/2}$$

$$\tan \theta = \frac{b}{a}$$

$$Z^* = a - jb = re^{-j\theta}$$

$$\operatorname{Re}(Z) = a$$

$$\operatorname{Im}(Z) = b$$

$$\text{Magnitude}^2 = |Z|^2 = ZZ^* = a^2 + b^2$$

$$\text{Argument} = \theta = \arctan\left(\frac{b}{a}\right)$$

$$\cos \theta = \frac{1}{2}(e^{j\theta} + e^{-j\theta})$$

$$\sin \theta = \frac{1}{2j}(e^{j\theta} - e^{-j\theta})$$

## Expansions

$$e^x = 1 + x + \frac{1}{2!}x^2 + \frac{1}{3!}x^3 + \dots$$

$$(1+x)^n = 1 + nx + \frac{n(n-1)}{2!}x^2 + \frac{n(n-1)(n-2)}{3!}x^3 + \dots$$

$$\text{Small } x: \quad (1+x)^n \approx 1 + nx \quad \sin x \approx x \quad \tan x \approx x \quad \cos x \approx 1$$

$$\text{Small } \Delta x \text{ in } x = x_0 + \Delta x: \quad f(x) \approx f(x_0) + \Delta x \left(\frac{df}{dx}\right)_{x_0}$$

# index

- Accelerated failure tests, 177  
Acceptors, 390, 461  
Accumulation, 370  
Accumulation region, 444  
Activated state, 98  
Activation energy, 98  
Activator, 820, 841  
  - excitation, 822  
Active device, defined, 570  
Affinity, electron, 375, 386, 462  
Allotropy, 61-63, 102  
  - transition temperature, 61  
Alloy, 178  
  - ternary, iii-v, 545  
Amorphous semiconductors, 78-82, 458-461  
  - bandgap, 460  
  - extended states, 458, 462  
  - localized states, 459, 463  
  - mobility edge, 460  
  - tail states, 460  
Anomalous solids, 78-82, 98-99  
Ampere's law, 693  
Angular momentum, 269  
  - intrinsic, 245-247  
  - orbital, 232  
  - potential energy, 249-250  
  - total, 252-253  
Anion, 6, 15, 99  
Anisotropic magnetoresistance (AMR), 744-748, 762  
Anisotropy, magnetocrystalline, 706-708  
  - shape, 725, 763  
Antibonding orbital, 286, 288  
Antiferromagnetism, 699, 759  
Antireflection coating, 570, 802-803  
Arrhenius rate equation, 47  
a-Si:H, 82, 459  
Aspect ratio, 175  
Atomic concentration, 55  
Atomic magnetic moments, 687-688  
Bohr magneton, 688, 759  
  - unfilled subshells, 688  
Atomic mass, 8  
Atomic mass number, 8  
Atomic mass units (amu), 8, 99  
Atomic number, 4  
  - effective ( $Z_{eff}$ ), 240  
Atomic packing factor (APF), 55, 99  
Atomic structure, 3-8  
  - orbital angular momentum quantum numbers, 4, 232, 270  
  - principal quantum number, 4, 232, 270  
  - shell, 4, 239  
  - subshells, 4, 239  
Atomic weight. See Atomic mass  
Attenuation, 841  
Attenuation coefficient, 841  
Attenuation in optical fibers, 817-819  
  - graph, 818  
  - Rayleigh scattering limit, 819  
Avalanche breakdown, 502-504, 570  
Avalanche effect, 503  
Average free time (in electron drift), 117.  
  - See also Mean free time  
Avogadro's number, 8, 25, 99  
  
B versus H, 716-717  
Balmer series, 278  
Balmer-Rydberg Formula, 245  
Band theory of solids, 291-299  
Bandgap (energy gap)  $E_g$ , 302, 355, 357, 375, 464  
  - direct band gap, 430, 451  
  - indirect band gap, 430, 452  
  - mobility gap, 460  
  - narrowing and emitter injection efficiency, 576  
  - temperature dependence, 467  
Bardeen-Cooper-Schrieffer photo, 731  
  - theory, 739  
Barkhausen effect, 715  
Basis, 50, 95, 99  
BCC (body centered cubic). See Crystal structure  
BCS theory. See Bardeen-Cooper-Schrieffer  
BCT (body centered tetragonal). See Crystal structure  
Bednorz, J. George, 684  
Beer-Lambert law, 428  
Biaxial crystals, 828  
  - negative, 828  
  - positive, 828  
Binary eutectic phase diagrams, 90-95  
Bipolar junction transistor, 475, 506-522, 570  
  -  $\alpha$ , 509-510  
  - active region, 511  
  - amplifier, CB, 515-517  
  -  $\beta$ , 510, 521  
  - base, 506  
  - base-transport factor,  $\alpha_T$ , 509-510  
  - base-current modulation, 512, 570. See also Early effect  
  - collector, 506  
  - collector junction, 507, 570  
  - common base (CB) configuration, 506-517  
  - common emitter (CE) DC characteristics, 517-518  
  - current gain  $\alpha$ , CB, 509-510  
  - current transfer ratio  $\alpha$ , 509, 514  
  - emitter, 506  
  - emitter injection efficiency, 513-514, 575  
  - emitter junction, 507, 571  
  - emitter current, 509  
  - equations, *ppm* BJT, 574-575  
  - input resistance, 516, 519  
  - power gain, 509  
  - saturated operating region, 518  
  - small signal equivalent circuit, 572  
  - small signal low-frequency model, 518-522  
  - transconductance, 520  
  - transistor action, 509  
  - transit time, minority carrier, 510  
  - voltage gain, 516, 520  
Birefringence. See also Retarding plates  
  - circular, 835-837  
  - crystals, 827, 841  
  - of calcite, 832-833  
  - of calcite crystal, photo, 828  
BJT. See Bipolar junction transistor  
Blackbody radiation, 201-205  
  - Planck's formula, 203  
  - Rayleigh-Jeans law, 203  
  - Stefan's black body radiation law, 203  
  - Stefan's constant, 203  
  - Wien's law, 277  
Black's equation, 177, 178  
Bloch wall, 706, 708-741, 759  
  - potential energy, 710  
  - thickness, 710  
Bloch wavefunctions, 450, 461, 462  
Bohr magneton, 280, 688, 759  
Bohr model, 3  
Bohr radius, 233, 239  
Bohr's correspondence principle, 217  
Boltzmann constant, 28  
Boltzmann energy distribution, 39  
Boltzmann factor, 38  
Boltzmann statistics, 312-313, 363, 479, 661  
Bond, general, 9-25  
  - energy, 11, 99  
  - length, 10  
  - polar, 22  
  - prismatic, 9-18, 102  
  - relative angle, 78  
  - secondary, 18P22, 102  
  - switching, 155  
  - twisting, 79  
Bonding and types of solids, 9-25  
Bonding (binding) energy, 11, 99  
Bohring orbital, 286, 288  
Bohron particle, 740  
Bound charges, 529  
Boundary conditions  
  - dielectrics, 614-620, 670  
  - electric field, 794  
  - magnetic field, 794  
  - quantum mechanics, 210  
Bragg diffraction condition, 198, 269, 356, 848-852  
  - Bragg angle, 849  
  - diffracted beam, 848  
  - diffraction angle, 849  
  - for cubic crystals, 851  
Bragg distributed reflector, 568  
Bragg's law. See Bragg diffraction condition  
Brems, 178, 182  
Breitwies lattices, 95-98  
  - unit cell geometry, 56, 97  
Bronze, 178  
Brewster's angle, 796, 841

- Brillouin zones, 355, 357-361  
 Buckminsterfullerene. *See* Carbon  
 Built-in field, 570  
 Built-in potential, 421-422, 478-480  
 Built-in voltage, 570  
 Bulk modulus, 99
- Capacitance**  
 definition, 584  
 per unit volume, 634  
 temperature coefficient (TCC), 636  
 volume efficiency, 634
- Capacitor**  
 constructions, 631-634  
 dielectric materials, 631  
 dielectrics table, 635, 678  
 electrolytic, 633  
 equivalent circuits for parallel and series, 676  
 polyester (PET), 636, 677  
 polymeric film, 632  
 tantalum, 634  
 temperature coefficient, 636  
 types compared, 631, 635, 678
- Carbon**, 61-63  
 amorphous, 63  
 Buckminsterfullerene, 61-62  
 diamond, 61, 62  
 graphite, 61, 62  
 lonsdaleite, 62  
 properties (table), 63  
 Carbon nanotube (CNT), 63, 336, 370  
 field enhancement factor, 370
- Carrier concentration**  
 majority carrier, 410  
 minority carrier, 410  
 of extrinsic semiconductor, 388-392  
 of intrinsic semiconductor, 380-387  
 saturation temperature, 397  
 temperature dependence of, 396-401  
   extrinsic range, 398  
   intrinsic range, 398  
   ionization range, 397
- Cathode**, 363
- Cathodoluminescence**, 335, 820, 841
- Cation**, 6, 15, 99
- Cauchy coefficients (table)**, 782
- Cauchy dispersion equation**, 783, 784
- CB. *See* Conduction band**
- Ceramic**, magnets, 726
- Ceramic materials**, 22
- Chemisorption**, 74
- Chip (integrated circuit)**, 570
- Circular birefringence**, 835-837, 841  
 media, 836  
 optical activity, 835  
 specific rotary power, 836, 844
- Cladding**, 791
- Clausius-Mossotti equation**, 593-594, 602, 670
- Coaxial cable failure**, 628-631  
   thermal breakdown, 678-679
- Coercive field (coercivity)**, 715, 759
- Cohesive energy**, 17
- Cole-Cole plots**, 611-614
- Collimated beam**, 36
- Common Base (CB) BJT configuration**.  
*See* Bipolar junction transistor
- Compensated semiconductor**, 461
- Compensation doping**, 392-396, 461, 465
- Complementary principle**, 269
- Complex dielectric constant**, 605-611, 804-811  
   loss angle, 610  
   loss tangent, 607  
   relaxation peak, 607  
   Complex propagation constant, 805, 842
- Complex refractive index**, 804-811, 842, 845-847  
   extinction coefficient, 805, 842  
   for  $n$ -Si, 806  
   of InP, 808  
   resonance absorption, 809-811  
**Complex relative permittivity. *See* Complex dielectric constant**
- Compton effect**, 269
- Compton scattering**, 199-202
- Conduction**, 114-122, 416-422  
   in metals, 318-320  
   in semiconductors, 378-380  
   in silver, 319
- Conduction band (CB)**, 302, 374-378, 461
- Conduction electron concentration**, 115, 148
- Conduction electrons**, 115, 155, 181, 299
- Conduction in solids**  
   electrical, 113-148  
   thermal, 149-154  
   in thin films, 166-167
- Conductivity**  
   activation energy for, 161  
   electrical, 178, 180-181  
   of extrinsic semiconductor, 389  
   of Fermi level electrons in metal, 318  
   of intrinsic semiconductor, 380  
   of ionic crystals and glasses, 159-162  
   lattice-scattering-limited, 124  
   of metals, 114, 350-352, 367  
   of nonmetals, 154-162  
   of semiconductors, 155-159  
   temperature dependence of, 122-125, 404-406
- Conductivity-mixture rule**, 140
- Contact potential**, 320-322
- Continuity equation**, 422-427  
   steady state, 424-427  
   time-dependent, 422-423
- Continuous random network (CRN)**  
   model, 79
- Cooper pairs**, 740, 759
- Coordination number (CN)**, 12, 17  
   definition, 99
- Core**, 791
- Corona discharge**, 622, 670
- Covalent bond**, 99
- Covalent solids**, 595-596
- Covalently bonded solids**, 11-13
- Critical angle**, 842
- Critical electric field**, 571
- Crystal**, 99
- Crystal directions and planes**, 56-61, 110
- Crystal lattice**, 49-63  
   different types, 97
- Crystal periodicity**, 49  
   strained around a point defect, 66
- Crystal structure**, 50  
   body-centered cubic (BCC), 51, 97, 109  
   body-centered tetragonal (BCT), 97, 98  
   close-packed, 13, 51  
   CsCl, 54  
   diamond cubic, 52, 109  
   face-centered cubic (FCC), 14, 50, 55, 97, 100  
   diffraction pattern (figure), 852  
   hexagonal close-packed (HCP), 51  
   NaCl, 51-53  
   polymorphic, 61  
   properties (table), 54  
   study using x-ray diffraction, 849-852  
   Laue technique, 850  
   powder technique, 851  
   types, 49-56, 97  
   zinc blende (ZnS), 53, 109
- Crystal surface**, 73-76  
   absorption, 74  
   adsorption, 74  
   chemisorption, 74  
   dangling bonds, 74, 81  
   Kossel model, 74  
   passivating layer, 74  
   physisorption (physical adsorption), 74  
   reconstruction, 74  
   terrace-ledge-kink model, 74
- Crystal symmetry**, 98
- Crystal systems**, 98
- Crystal types**, 49-56
- Crystalline defects**, 64-76
- Crystalline solid**, 49
- Crystalline state**, 49-63
- Crystallization**, 99  
   from melt, 70  
   nuclei, 70
- Cubic crystals**, 97  
   interplanar separation, 851
- Cubic symmetry**, 50
- Curie temperature**, 648, 650, 670, 703-704  
   table, 704
- Curie-Weiss law**, 697
- Current in plane (CIP)**, 747
- Czochralski growth**, 76-77
- Dangling bonds**, 81
- De Broglie relationship**, 205-207, 269
- Debye equations**, 611-614, 670  
   non-Debye relaxation, 614
- Debye loss peak**, 612
- Debye heat capacity**, 342-348
- Debye frequency**, 344, 363
- Debye temperature**, 344, 363  
   table, 346
- Defect structures**, 75-76
- Deformation, plastic (permanent)**, 69
- Degeneracy**, 230
- thick-fold**, 230
- Degenerate semiconductor**, 406, 461
- Degree of freedom**, 28
- Delocalized electrons**, 13  
   electron cloud or gas, 13, 295
- Demagnetization**, 717-719
- Density of states**, 305-311, 315-316, 363, 380-382, 429  
   effective density at CB edge, 382, 461  
   effective density at VB edge, 382
- Density of vibrational states**, 364
- Depenning. *See* Demagnetization**
- Depletion capacitance**, 498-499, 564
- Depletion region. *See* pn junction**
- Depolarizing field**, 657-658  
   depolarizing factor, 657
- Diamagnetism**, 696-698  
   depurting, 748
- Dichroism**, 833
- Dielectric breakdown**, 620-631  
   aging effects, 621  
   breakdown mechanisms compared, 628  
   in coaxial cables, 628-631, 678-679  
   electrical tree, 626  
   electrofractive, 624-625, 671  
   electromechanical, 624-625, 671  
   electron avalanche breakdown, 623  
   electronic, 623-624, 671  
   external discharges, 627-628, 671  
   in gases, 621-622  
   internal discharges, 625-626, 671  
   intrinsic, 623-624, 671  
   in liquids, 622-623  
   lets, 603-611  
   partial discharge, 621-622, 672  
   in solids, 623-631  
   surface tracking, 628, 671, 672  
   table, 621



- Dielectric breakdown—Cont.  
 thermal, 624, 673  
 water treac, 627
- Dielectric materials, 583–683  
 constant. *See* Relative permittivity  
 definition, 670  
 dispersion relation, 666  
 loss, 603–611, 670  
 loss table, 611  
 low- $k$ , 175  
 properties (table), 678  
 strength, 584, 620–621, 670. *See also*  
 Dielectric breakdown  
 strength table, 621  
 volume efficiency, 634
- Dielectric mirrors, 803, 842
- Dielectric mixtures, 667–669  
 effective dielectric constant, 667  
 Lichteneker formula, 668  
 logarithmic mixture rules, 668  
 Maxwell-Garnett formula, 669
- Dielectric resonance, 607, 662–667, 670  
 frictional force, 663  
 Lorenz dipole oscillator model, 664  
 natural angular frequency, 664  
 peak, 665  
 relaxation peak, 665  
 resonant angular frequency, 664  
 restoring force, 663  
 spring constant, 663
- Diffraction, 269, 848–852. *See also* Bragg  
 diffraction condition  
 angle, 849  
 beam, 848  
 patterns (figure), 193, 852  
 study of crystal structure, 352–361,  
 849–852
- Diffraction, 851
- Diffusion, 46–49, 99, 416–422, 461, 571  
 coefficient, 48, 99, 420  
 current, 484  
 current density, 416, 418  
 diffusion length, 424, 427, 483  
 mean free path, 416–417
- Diffusion capacitance, 500–502, 571
- diode action, 501  
 dynamic conductance, 501  
 dynamic (incremental) resistance,  
 500, 571
- Diffusion coefficient, 420
- Diode. *See* pn Junction  
 action, 501  
 equation, 488  
 laser, 266–269  
 long, 572  
 photodiodes, 564–566  
 short, 486, 572
- Dipolar (orientational) polarization,  
 598–600, 660–662, 670  
 Langevin function, 661–662  
 relaxation equation, 670  
 relaxation process, 604, 670  
 relaxation time, 604
- Dipole moment. *See* Electric dipole  
 moment; Magnetic dipole moment
- Dipole relaxation, 604–607, 670
- Dipole-dipole interaction, 20–21
- Dirac, Paul Adrian Maurice, 314
- Direct recombination capture  
 coefficient, 469
- Dislocations, 68–70, 99  
 edge, 68, 99  
 screw, 69, 102
- Dispersion relation, 364, 666, 842. *See*  
*also* Refractive index
- Dispersive medium, 785, 842
- Domains. *See* Ferromagnetism
- Dones, 389, 461
- Doping, 388–396  
 compensation, 392–394  
*n*-type, 384, 388–390  
*p*-type, 384, 390–392
- Doppler effect, 265, 269
- Double-heterostructure (DH) device, 547
- Drift mobility, 117, 401–404  
 definition, 178  
 due to ionic conduction, 162  
 effective, 127, 403  
 impurity dependence, 401–404  
 impurity-scattering-limited, 127, 403, 462  
 lattice-scattering-limited, 127, 402, 463  
 tables, 146, 386  
 temperature dependence, 401–404
- Drift velocity, 114, 118, 121, 157,  
 178, 379
- Drude model, 114–122, 319
- Dulong-Petit rule, 30, 344
- Dynamic (incremental) resistance,  
 500–502, 571
- Early effect, 512, 570
- Early voltage, 538
- Eddy currents and losses, 760, 766
- Effective mass, 303–305, 364, 379,  
 453–455, 462
- EHP. *See* Electron-hole pairs
- Eigenenergy, 214
- Eigefunction, 210
- Einstein relation, 188, 419, 462
- E-I diagrams, 448–452
- Elastic modulus, 24–25, 100
- Electric dipole moment, 19, 100, 583,  
 585–589, 670  
 definition, 19, 100, 670  
 induced, 20, 586, 779–780  
 in nonuniform electric field, 674–675  
 permanent, 15, 19, 598  
 relaxation time, 604
- Electric displacement, 654–658  
 depolarizing factor, 657  
 depolarizing field, 657
- Electric susceptibility, 591, 671
- Electrical conductivity, 178, 180–181
- Electrical contacts, 143–144
- Electrical noise, 42–45, 108. *See also* Noise  
 Johnson resistor noise equation, 44  
 rms noise voltage, 44
- Electrochemical potential, 321
- Electrodeposition, 167
- Electroluminescence, 544, 820, 843  
 injection, 823
- Electromechanical coupling factor, 642
- Electromigration, 172  
 accelerated failure tests, 177  
 of Al-Cu interconnects, 189  
 barrier, 177  
 definition, 178  
 hillock, 177  
 mean time to 50 percent failure, 177  
 rate, 177  
 void, 177
- Electromigration and Black's equation,  
 176–177
- Electron  
 average energy in CB, 385, 462  
 average energy in metal, 317, 363  
 concentration in CB, 382, 388–390, 392  
 conduction electrons, 115, 155, 181, 299  
 confined, 212–217  
 crystal momentum 451, 454, 813–814  
 current due to, 419  
 diffraction in crystals, 352–361  
 diffraction patterns, 206  
 diffusion current density, 418  
 effective mass, 303–305, 364, 379,  
 453–455, 462  
 effective speed in metals, 317  
 energy in hydrogenic atom, 236–241  
 energy in metals, 317  
 Fermi-Dirac statistics, 123  
 gas, 295  
 group velocity, 454  
 magnetic dipole moment, 248–252  
 mean recombination time (pn junction),  
 487  
 mobility, 379  
 momentum, 214  
 motion and drift, 452–453  
 in a potential box, 228–230  
 spin, 245–247, 271  
 spin resonance (ESR), 280  
 standing wave, 353  
 surface scattering, 168–172  
 as a wave, 205–212, 352–354  
 wavefunction in hydrogenic atom,  
 231–236  
 wavefunction in infinite PE well, 229  
 wavelength, 207
- Electron affinity, 6, 100, 375, 436, 462
- Electron beam deposition, 80, 167
- Electron drift mobility. *See* Drift mobility
- Electron spin resonance (ESR), 280
- Electronegativity, 22, 100
- Electron-hole pairs, 376–378  
 generation, 302, 376–378, 383, 410–414  
 mean thermal generation time, 490  
 recombination, 377–378, 412, 457–458
- Electronic impurity, 546
- Electronic (quasium) state, 234, 247
- Electro-optic effects, 837–841, 842  
 field induced refractive index, 838  
 Kerr effect, 838, 842  
 noncentrosymmetric crystals, 838  
 Pockels effect, 838, 843
- Electroosmosis, 431, 463
- Energy bands, 291–295, 305–308
- Energy density, 269, 695
- Energy gap ( $E_g$ ). *See* Bandgap
- Energy, quantized, 214, 236–241  
 ground state energy, 215  
 in the crystal, 462  
 infinite potential well, 230
- Energy versus crystal momentum plot. *See*  
*E-I diagrams*
- Epitaxial layer, 544, 571
- Equilibrium, 100
- Equilibrium state, 41, 100
- Eutectic composition, 93, 100
- Eutectic phase diagrams, 90–95
- Eutectic point, 91
- Eutectic transformation, 92
- Evanescence wave, 798  
 attenuation coefficient, 798  
 penetration depth, 799
- Excess carrier concentration, 410, 462,  
 468–469
- Exchange integral, 702
- Exchange interaction, 700–703, 760
- Excitation  
 activator, 822  
 host, 822
- Excited atom, 6
- Extended states, 458, 462
- External quantum efficiency, 571
- External reflection, 798, 801–802, 846
- Extinction coefficient, 805, 842
- Extrinsic semiconductors, 388–396, 462,  
 464–465
- Family of directions in a crystal, 58
- Family of planes in a crystal, 59
- Fermi energy, 294, 314, 317, 320–322,  
 364, 366, 435–436, 462  
 in intrinsic semiconductor, 384

- in a metal, 315-317  
table, 295
- Fermi surface, 359
- Fermi-Dirac statistics, 123, 312-315, 364
- Ferrimagnetism, 700, 760
- Ferrite antenna, 767-768
- Ferrites, 723, 760, 767-768. *See also* Ferrimagnetism
- Ferroelectric crystals, 647-653, 671
- ferroelectric axis, 649
- Ferromagnetism, 699, 760
- closure domains, 706
- domain wall energy, 709-711, 760, 764-765
- domain wall motion, 712-713
- domain walls, 706, 708-711, 760
- domains, 699, 705-706, 761
- electromagnetic interaction energy, 701
- energy band model, 742-744
- magnetocrystalline anisotropy, 706-708
- materials table, 704
- ordering, 699
- origin, 700-703
- polycrystalline materials, 713-717
- Fick's first law, 418
- Field assisted tunneling probability, 334
- Field effect transistor, 571. *See* JFET; MOSFET
- Field emission, 332-337, 364
- Field emission tip, 335
- anode, 335
- gate, 335
- Spindt tip cathode, 335
- Field enhancement factor, 370
- Fluence
- energy, 275
- photon, 276
- Fluorescence, 820, 842
- Flux, defined, 269
- luminous, 853
- of particles, 416
- of photons, 198, 853
- photometric, 853
- radiant, 853
- Flux quantization, 758-759
- Forward bias, 487-489. *See also* pn Junction
- Fourier's law, 150, 178
- Fowler-Nordheim
- anode current, 335
- equation, 334
- field emission current, 370
- Fraunhofer, 244-245
- Free surface charge density, 592
- Frenkel defect, 66, 100
- Fresnel's equations, 793-803, 842
- Fresnel's optical indicatrix, defined, 829-832, 843
- extraordinary wave, 829
- ordinary wave, 829
- Frequency, resonant
- antiresonant, 645
- mechanical resonant, 645
- natural angular frequency, 664
- resonant angular frequency, 664
- Fuchs-Sondheimer equation, 170
- GaAs, 52, 386, 466
- Gas constant, 25
- Gas pressure (kinetic theory), 27
- Gauge factor, 434
- Gauss's law, 614-620, 654-658, 671
- Giant magnetoresistance (GMR), 744-748, 751, 760. *See also* Magnetoresistance table, 747
- Classes, 78-82. *See also* Amorphous solids
- melt spinning, 79
- GMR. *See* Giant magnetoresistance
- Grain, 70, 100
- Grain boundaries, 70-73, 100
- disordered, 72
- Grain coarsening (growth), 73
- Ground state, 215, 269
- energy, 215, 237
- Group index, 784-787, 842
- definition, 785
- Group velocity, 364, 784-787, 842
- in medium, 785
- in vacuum, 785
- Grüneisen's model of thermal expansion, 361-363
- Grüneisen's law, 362, 371
- Grüneisen's parameter (table), 363
- Gyromagnetic ratio, 687
- Hall coefficient, 146, 178, 359
- for ambipolar conduction, 158
- for intrinsic Si, 158-159
- Hall devices, 145-148
- Hall effect, 145-148, 178, 185-186
- in semiconductors, 156-159, 468
- Hall field, 146
- Hall mobility, 148
- Hard disk storage, 750-752
- magnetic bit tracks, 751
- magnetoresistance sensor, 751
- thin film heads, 752
- Hard magnetic materials, 724-729, 761
- design, 768-769
- neodymium-iron-boron, 727
- rare earth cobalt, 726-727
- single domain particles, 724, 761
- table, 724
- Harmonic oscillator, 337-342, 364
- average energy, 343
- energy, 338
- potential energy of, 338
- Schrödinger equation, 338
- zero point energy, 339, 365
- Heat, 41, 100
- Heat capacity, 28, 100
- Heat current, 153
- Heat of fusion, 84
- Heat, thermal fluctuation and noise, 40-45
- noise in an RLC circuit, 44
- rms noise voltage, 44
- thermal equilibrium, 40
- Heisenberg's uncertainty principle, 217-220, 269, 277
- for energy and time, 219
- for position and momentum, 218
- Helium atom, 254-256
- Helium-neon laser, 261-264
- efficiency, 264
- Hervé-Vandamme relationship, 845
- Heterogeneous media, 667-669
- Lichtenecker formula, 668
- logarithmic mixture rules, 668
- Maxwell-Garnett formula, 669
- Heterogeneous mixture (multiphase solid), 139-143, 178
- Heterojunction, 547, 571
- Heterostructure devices, 544, 547
- confining layers, 548
- double heterostructure, 547
- Hexagonal crystals, 52, 97
- HF resistance of conductor, 163-166
- Hole, 155, 302, 373, 376-378, 455-456
- concentration in VB, 382, 391-392
- current due to, 419
- diffusion current density, 418
- diffusion length, 483
- effective mass, 380, 456
- mean recombination time (pn junction), 487
- mobility, 380
- Homogeneous mixture, 178-179
- Homojunction, 547, 571
- Host excitation, 822
- Host matrix, 820, 843
- Human eye, 273-275
- photopic vision, 273
- scotopic vision, 273
- Hand's rule, 256-258, 269, 281
- Hybrid orbital, 300
- Hybridization, 300
- Hydrogen bond, 19
- Hydrogenated amorphous silicon. *See* a-Si:H
- Hydrogenic atom, 231-253
- electron wavefunctions, 231-236
- line spectra, 278
- Hysteresis loop, 715-719, 761
- energy dissipated per unit volume, 718-719
- loss, 761, 766
- Image charges theorem, 332
- Impact ionization, 503, 571
- Inparities, 64-66
- Incanescence, 820
- Inductance, 163, 693-694
- of a solenoid, 763
- toroid, 694, 723, 765
- Infinitesimal potential well, 212-217
- Insulation strength. *See also* Dielectric breakdown
- aging, 627, 671
- Integrated circuit (IC), 571
- Intensity, defined, 269
- of EM waves, 192
- of light, 192, 197-198, 799
- Interconnects, 172-176, 179, 188
- aspect ratio, 175
- effective multilevel capacitance, 174
- low-k dielectric materials, 175
- multilevel interconnect delay time, 175
- RC time constant, 173, 175-176
- Interfacial polarization. *See* Polarization
- Internal discharges. *See* Dielectric breakdown
- Internal reflection, 796-797, 800-801, 846
- Interplanar separation in cubic crystals, 851
- Interstitial site, 45, 101
- impurity, 66, 83-84
- Intrinsic angular momentum. *See* Angular momentum; Spin
- Intrinsic concentration ( $n_i$ ), 383, 462, 485
- Intrinsic semiconductors, 374-387, 462
- Inversion, 532-535, 571. *See also* MOSFET
- Ion implantation, 541-543, 571
- Ionic conduction, 179
- Ionic crystals, 17
- ionically bonded solids, 14-18, 104
- table, 21
- Ionization energy, 6, 15, 101, 237, 462
- for  $n$ th shell, 237
- of He<sup>+</sup>, 240
- Irradiance, 787-789
- average, 788, 842
- instantaneous, 788, 842
- Isoelectronic impurity, 546, 572
- Isomorphous, 101
- Isomorphous alloys, 83-88
- Isomorphous phase diagram, 84, 179
- Isotropic substance, 101

- JFET, 522-532, 571  
 amplifier, 528-532, 577  
 channel, 523, 570  
 characteristics, 524, 528  
 common source amplifier, 529  
 constant current region, 528  
 current saturation region, 528  
 drain, 522  
 drain current, 523  
 field effect, 528  
 gate, 522  
 general principles, 522-528  
 nonlinearity, 532  
 pentode region, 528  
 pinch-off condition, 525-526  
 pinch-off voltage, 524, 572, 576-577  
 quiescent point, 529  
 source, 522  
 transconductance, 531  
 voltage gain, small-signal, 531  
 Johnson resistor noise equation, 44  
 Josephson effect, 756-758  
 dc characteristics, 757  
 definition of  $I_c$ , 758  
 Joule's law, 179  
 Junction field effect transistor. *See* JFET
- i.* *See* Wavevector  
 Kameclingh Onnes, Heike, 730  
 Kerr effect, 838, 842  
 coefficients, table, 840  
 Killy, Jack, 474  
 Kinetic (molecular) theory, 25-36, 101  
 degree of freedom, 28  
 equipartition of energy theorem, 28  
 heat capacity, 28. *See also* Dulong-Petit rule  
 mean kinetic energy, 27-28  
 mean speed, 27, 30-31, 115  
 thermal fluctuations, 40-45  
 Kossel model, 74  
 Kraters-Kronig relations, 806, 842-843
- Lamellae, 93  
 Langmuir function, 661-662  
 Lasers, 258-267, 269-270  
 cavity modes, 265  
 diode, 266-269  
 Doppler effect, 265  
 He-Ne laser. *See* Helium-neon laser  
 lasing emission, 261  
 linewidth, 265  
 long-lived states, 260  
 metastable state, 260  
 output spectrum, 265-267  
 population inversion, 259  
 pump energy level, 260  
 pumping, 260, 270  
 semiconductor, 475, 566-569  
 single-frequency, 569  
 single-mode, 569  
 stimulated emission, 259, 271  
 threshold current, 569
- Lattice, 50, 95, 101. *See also* Bravais lattices  
 cut-off frequency, 340  
 energy, 18  
 parameter, 50, 56, 96, 101  
 space, 95  
 waves, 337-342, 347, 364  
 Lattice vibrations, 339-350  
 density of states, 343, 363  
 heat capacity, 344  
 internal energy, 343  
 modes, 341-342, 364  
 state, 341, 364  
 Lattice-scattering-limited conductivity, 174
- Laser technique, 830  
 Law of the junction, 482-483, 572  
 Leonard-Jones 6-12 potential energy curve, 23  
 Lever rule, 144  
 Lichtencker formula, 668  
 Light absorption, 804-811  
 and conductivity, 808  
 Light as wave, 191-194  
 Light emitting diodes (LEDs), 475, 543-551  
 characteristics, 548-551  
 electroluminescence, 544  
 external efficiency, 546  
 heterojunction high intensity, 547-548  
 linewidth, 549, 572, 579  
 materials, 546  
 principles, 543-546  
 spectral linewidths, 550-551, 579  
 substrate, 544  
 turn-on (cut-in) voltage, 550, 573  
 Light propagation, 804-805  
 attenuated, 805  
 conduction loss, 805  
 lossless, 804  
 Light scattering, 804, 816-817, 844  
 Light waves, 774-776  
 Line defects, 68-70  
 strain field, 68  
 Linear combination of atomic orbitals (LCAO), 287, 364  
 Liquids curve, 85  
 Local field, 593-594, 658-660, 671-672  
 Localized states, 459, 463  
 Long range order, 49, 78  
 Lomdaleite, 62  
 Lorentz dipole oscillator model, 664  
 Lorentz equation, 658-660  
 Lorentz field, 593-594  
 Lorentz force, 145, 179  
 Lorentz number, 150. *See also* Wiedemann-Franz-Lorentz's law
- Loss angle, 610  
 Loss tangent (factor), 607, 672  
 Lumera, 853  
 Luminescence, 820-825  
 activator, 820, 841  
 activator excitation, 822  
 cathodoluminescence, 820, 843  
 electroluminescence, 544, 820, 843  
 fluorescence, 820, 842  
 host excitation, 822  
 host matrix, 820, 843  
 phosphorescence, 821, 843  
 photoluminescence, 820, 843  
 radiative recombination center, 822  
 Stoke's shift, 822, 844  
 X-ray, 820  
 Luminescent (luminescence centers). *See* Activator
- Luminous efficacy, 854  
 Luminous (photometric) flux or power, 270, 273, 853  
 lumen, 853  
 Lyman series, 278
- Madelung constant, 17  
 Magnet, permanent, 768  
 table, 768  
 with yoke and air gap, 768-769  
 Magnetic bit tracks, 751  
 Magnetic dipole moment, 685-686, 761  
 atomic, 687-688  
 definition, 686  
 of electron, 248-252  
 orbital, 249, 687  
 per unit volume, 689  
 potential energy, 249-250  
 spin, 249, 687
- Magnetic domain. *See* Ferromagnetism  
 Magnetic field (B), 179, 761, 787-789  
 in a gap, 771  
 intensity, 691-692  
 transverse, 793  
 Magnetic field intensity (strength). *See* Magnetizing field (H)  
 Magnetic flux, 693, 761  
 quantization, 758-759  
 Magnetic flux density. *See* Magnetic field  
 Magnetic induction. *See* Magnetic field  
 Magnetic materials classification, 696-700  
 amorphous, 722  
 soft and hard materials, 719-721  
 table, 697  
 Magnetic moment. *See* Magnetic dipole moment  
 Magnetic permeability, 179, 692-696, 761. *See also* Relative permeability quantities table, 693  
 relative, 692, 762  
 Magnetic pressure, 769-770  
 Magnetic quantities and units, table, 693  
 Magnetic quantum number, 232, 270  
 Magnetic recording, 749-756  
 fringing magnetic field, 749, 771  
 general principles, 749-750, 770-771  
 hard disk storage, 750-752  
 head materials, 752-753  
 inductive recording heads, 749  
 longitudinal recording, 749  
 magnetic bit tracks, 751  
 materials tables, 754, 755  
 storage media, 753-756, 770-771  
 thin film heads, 752  
 Magnetic susceptibility, 692-696, 762  
 Magnetism and energy band diagrams, 740-744  
 Energy band model of ferromagnetism, 742-744  
 Pauli-Spin paramagnetism, 740-742  
 Magnetization current, 690, 762  
 Magnetization of matter, 685-696  
 Magnetization vector (M), 688-690, 762  
 and surface currents, 690, 762  
 Magnetization versus H, 713-717  
 coercivity, 715, 759  
 initial magnetization, 716  
 remanent (residual), 715, 762-763  
 saturation, 703-704, 717, 763  
 Magnetizing field (H), 691-692, 761  
 conduction current, 691  
 Magnetocrystalline anisotropy, 706-708, 762  
 easy direction, 706, 708, 760  
 energy, 708, 762  
 hard direction, 708, 761  
 Magnetometer, 179  
 Magnetoresistance, anisotropic and giant, 744-748, 762  
 current in plane (CIP), 747  
 ferromagnetic layer, 745  
 spacer, 745  
 spin valve, 747  
 Magnetostatic energy, 705, 762  
 density, 696  
 per unit volume, 694-696  
 Magnetostriiction, 711-712, 762  
 saturation strain, 711  
 Magnetostriictive energy, 711, 762  
 constant, 711  
 Majority carrier, 410, 463  
 Mass action law (semiconductors), 383, 463  
 with bandgap narrowing, 576  
 Mass fractions, 8-9, 88



- Mathiessen's rule, 125-134, 179, 181  
combined with Nordheim's rule, 137, 142-143
- Maxwell's equations, 774
- Maxwell-Boltzmann distribution function, 37-39
- Maxwell's principle of equipartition of energy, 28, 42-43
- Mayadas-Shatzkes formula, 168
- Mean free path  
of electron, 122, 123, 179  
in polycrystalline sample, 168  
in thin film, 169  
of gas molecules, 106-107
- Mean free time, 117, 119, 121, 179
- Mean frequency of collisions, 118
- Mean kinetic energy and temperature, 25-31
- Mean scattering time. *See* Mean free time
- Mean speed of molecules, 39-40
- Mean square free time, 121
- Mean thermal expansion coefficient, 35
- Mechanical work, 101
- Meissner effect, 731, 762
- Melt spinning, 79
- Metallic bonding, 13, 101
- Metallurgical junction (semiconductors), 476, 572
- Metal-metal contacts, 320-322
- Metal-oxide semiconductor (MOS), 532-535, 572. *See also* MOSFET  
threshold voltage, 539-541, 573
- Metal-oxide semiconductor field effect transistor. *See* MOSFET
- Metals, band theory, 352-361  
free electron model of, 315-317  
quantum theory of, 315-320
- Miller indices, 58-61, 101
- Minority carrier, 410-416, 463  
diffusion, 483  
diffusion length, 463  
excess concentration of, 410-416  
injection, 407-416, 475, 481-483, 572  
lifetime, 412, 463  
profiles (hyperbolic), 574  
recombination time, 412, 573
- Miscibility, 101
- Mixed bonding, 22-25
- Mixture rules, 139-144, 184
- Mobility. *See* Drift mobility
- Mold number, 265
- Modern theory of solids, 285-371
- Molar fractions, 8
- Molar heat capacity, 28, 101, 343
- Mole, 8, 101
- Molecular orbital, 286
- Molecular orbital theory of bonding, 285-290  
hydrogen molecule, 285-289
- Molecular orbital wavefunction, 364
- Molecular solids, 21
- Molecular speeds, distribution (Sturm-Liouville), 36
- Molecular velocity and energy distribution, 36-40
- Monoclinic crystals, 97
- Moseley relation, 279
- MOSFET, 532-543, 572  
accumulation, 570  
amplifier, 577-578  
depletion layer, 532-534, 571  
early voltage, 538  
enhancement, 535-539, 571  
field effect and inversion, 532-535  
inversion layer, 534  
ion implanted, 541-543  
MOST, 572
- NMOS, 572
- PMOS, 572
- silicon gate technology, 542  
threshold voltage, 539-541, 573
- Moss's rule, 845
- Motion of a diatomic molecule, 28-29  
rotational, 28-29  
translational, 28-29
- Most-Jones equations, 324
- Müller, K. Alex, 684
- Multilevel interconnect  
delay time, 175  
effective capacitance, 174  
RC time constant, 175
- Nanotube, carbon, 63, 336, 370
- Natural (resonance) frequency of an atom, 780, 846
- Nearly free electron model, 449
- Néel temperature, 699
- Newton's second law, 25
- Nichrome, 135
- NMOS. *See* MOSFET
- Nondegenerate semiconductor, 406-407, 463
- Node, 215
- Noise, 40-45. *See also* Electrical noise
- Nonstoichiometry, 75-76
- Nordheim's coefficient, 136  
table, 136
- Nordheim's rule, 134-139, 179, 182  
combined with Mathiessen's rule, 137, 142-143
- Normalization condition in quantum mechanics, 214
- n-type doping, 388-390  
energy-band diagram, 389
- Nucleate (solidity), 84
- Ohm's law of electrical conduction, 118, 150
- Ohmic contacts, 443-448, 463
- Optic axis, 829-830, 843  
principal, 827-828, 843
- Optical absorption, 427-431, 804-811, 841  
absorption coefficient, 428, 813  
band-to-band (interband), 429, 813-816  
and conductivity, 808  
free carrier, 805, 847  
lattice, 811-812  
penetration depth, 429, 813  
Resistible absorption, 811  
upper cut-off wavelength, 813
- Optical activity, 835, 843  
specific rotary power, 836
- Optical amplifiers, 267
- Optical anisotropy, 827-833, 841
- Optical fiber, 791, 817-819  
attenuation in, 817-819  
cladding, 791  
in communications, 791-792  
core, 791
- Optical fiber amplifiers, 267-268  
Erbium (Er<sup>3+</sup> ion) doped, 267, 282  
long-lived energy level, 267
- Optical field, 774
- Optical indicatrix. *See* Fresnel's optical indicatrix
- Optical power. *See* Radiant power
- Optical properties of materials, 773-847
- Optical pumping, 260, 270
- Optically isotropic, media, 778  
crystals, 827
- Orbital, 234, 270, 364  
magnetic moment, 249
- Orbital wavefunction, 270, 364
- Oriental polarization. *See* Dipolar polarization
- Orthorhombic crystal, 97
- Parallel rule of mixtures, 140
- Paramagnetism, 698, 762  
Pauli spin, 740-742, 764
- Parity, 216  
even, 216  
odd, 216
- Partial discharge, 618, 621-622, 672
- Particle flux, 416-420
- Particle statistics. *See* Statistics
- Paschen  
curves, 677  
series, 278
- Passivated Emitter Rear Locally diffused cells (PERL), 561-562
- Passive device, defined, 572
- Pauli exclusion principle, 115, 254-256, 270, 312-313, 701
- Pauli spin magnetization, 698, 740-742, 764
- Pauling scale of electronegativity, 22
- PECVD. *See* Plasma-enhanced chemical vapor deposition
- Peltier coefficient, 447-448  
device, 444  
effect, 445, 463  
figure of merit (FOM), 471-472  
maximum cooling rate, 472
- Penetration depth, 429, 813
- Periodic array of points in space. *See* Crystal structure
- PERL. *See* Passivated Emitter Rear Locally diffused cells
- Permanent magnet,  $(BH)_{max}$ , 727-729
- Permeability, absolute, 692. *See also* Magnetic permeability; Relative permeability  
initial, 720-721, 761  
maximum, 720-721, 762  
relative, 692, 762
- Permittivity. *See* Relative permittivity
- Phase, 83, 101, 179  
cored structure, 87  
diagrams, 84-88, 101  
equilibrium, 87  
eutectic, 90-95  
lever rule, 87  
liquidus curve, 85  
nonequilibrium cooling, 87  
solidus curve, 85  
tie line, 88
- Phonons, 337-352, 364, 409, 463, 815  
dispersion relation, 340, 364  
energy, 340  
group velocity, 341  
lattice cut-off frequency, 340  
momentum, 340, 815  
phosphor, 820-825, 843  
table, 824
- Photofluorescence, 821, 843
- Photoconductivity, 414-416, 463
- Photodetectors, 475
- Photodiodes, 564-566
- Photoelectric effect, 194-199, 270, 276
- Photogeneration, 376, 410-412, 463  
carrier kinetic energy, 473  
steady state rate, 469
- Photoinjection, 463
- Photometric flux. *See* Luminous flux or power
- Photometry, 853
- Photon, 191-205, 270, 272  
efficiency, quantum, 276  
energy, 196, 200  
flux, 198, 853  
momentum, 199, 200  
picture, 198



- Photon amplification, 258-261  
 Photovoltaic devices, principles, 551-559.  
   *See also* Solar cell  
 Photoresponse time, 413-414  
 Physical vapor deposition (PVD), 167  
 Physiosorption, 74  
 Piezoelectric  
   antiresonant frequency, 645  
   bender, 680  
   coefficients, 641, 681  
   detectors, 681  
   electromechanical coupling factor, 642  
   inductance, 646  
   materials, 672  
   mechanical resonant frequency, 645  
   poing, 643, 672  
   properties table, 642  
   quartz oscillators and filters, 644-647  
   spark generator, 643-644  
   transducer, 641, 673  
   voltage coefficient, 644, 680  
 Piezoelectricity, 638-647  
   center of symmetry, 639  
   nanosymmetric, 640  
 Piezoresistive strain gauge, 434-435  
 Piezoresistivity, 431-435, 463, 470  
   Cantilever equations, 470  
   diaphragm, 434  
   piezoresistive coefficient, 433, 463  
 pin Diodes, 564-566  
   depletion layer capacitance, 564  
 Pinch-off, 524-528, 537, 572, 576-577  
 Planar concentration of atoms, 60, 101,  
   109-110  
 Planar defects, 70-73  
 Planck, Max, 203  
   constant, 196  
 Plane of incidence, 793  
 Plasma-enhanced chemical vapor  
   deposition (PECVD), 82  
 PLZT, 672  
 PMOS. *See* MOSFET  
 pn Junction, 476-493  
   band diagram, 494-498  
   built-in potential, 478-480  
   depletion capacitance, 498-499, 571  
   depletion region, 477, 571  
   depletion region width, 479, 498  
   diffusion capacitance, 500-502  
   diffusion current, 481-487  
   forward bias, 481-487, 571  
   heterojunction, 547  
   homojunction, 547  
   ideal diode equation, 485  
   ideality factor, 488  
   incremental resistance, 500-502  
   I-V characteristics, 497  
   I-V for Ge, Si and GaAs, 486, 489  
   no bias, 476-481  
   recombination current, 488, 572  
   reverse bias, 489-493  
   reverse saturation current, 485, 490,  
   572  
   short diode, 486  
   space charge layer (SCL), 477, 571  
   storage capacitance. *See* Diffusion  
   capacitance  
   temperature dependence, 574  
   total current, 487-489  
   total reverse current, 491  
 pu Junction band diagrams 494-498  
   built-in voltage from band diagrams,  
   498  
   forward and reverse bias, 495-498  
   open circuit, 494-495  
 Pockels cell phase modulator, 840, 847  
 Pockels effect, 838, 843  
   coefficients, table, 840  
 Point defects, 64-68  
   Frenkel, 66  
   impurities, 64-68  
   interstitial, 66  
   Schottky, 66  
   substitutional, 65  
   thermodynamic, 64  
 Poisson ratio, 186  
 Polar molecules, 19  
 Polarizability, 586, 588, 781. *See*  
   Polarization  
   defined, 586, 672  
   dipolar (orientational), 662  
   ionic, 664  
   orientational, 662  
   table, 588  
 Polarization, 101, 583-603  
   charges, 591  
   definition, 585-586, 672  
   dipolar, 598-600, 660-662, 670  
   electronic, 585-589, 595-596, 671,  
   781  
   electronic bond, 671  
   induced, 586, 664, 671  
   interfacial, 600-601, 671  
   ionic, 597-598, 602, 662-667, 671,  
   811  
   mechanisms, 597-603  
   orientational. *See* Polarization, dipolar  
   relaxation peak, 665  
   table, 602  
   total, 601-603  
   vector, 589-593, 672  
 Polarization angle. *See* Brewster's angle  
 Polarization modulator, 841  
   halfwave voltage, 841  
 Polarization of EM wave, 796, 825-827,  
   843  
   circular, 826, 841  
   elliptical, 827  
   linear, 796, 825  
   plane, 825  
 Polarized molecule, 20  
 Poling, 643, 672  
 Polycrystalline films and grain boundary  
   scattering, 167-168  
 Polymorphism, 61, 102  
 Polysilicon gate (poly-Si), 541-543, 572  
 Population inversion, 259, 270. *See also*  
   Lasers  
 Powder technique, 851  
 Poynting vector, 787-789, 843  
 Primary  $\alpha$ , 94  
 Primary bonds, 18  
 Principal optic axis, 827-828  
 Principal refractive index, 827  
 Probability. *See* Statistics  
 Probability of electron scattering, 119  
 Probability per unit energy, 39  
 Proelectric (primary  $\alpha$ ), 94  
 Properties of electrons in a band,  
   296-299  
 Property, definition, 102  
 p-type doping, 390-392  
   energy-band diagram, 391  
 Pumping, 250, 270  
 PV work, 101  
 Pyroelectric, crystals, 647-653  
   coefficients, 650  
   current density, 652  
   current responsivity, 652  
   detector, 651-652, 681-682  
   electric time constant, 682  
   material, 672  
   table, 650  
   thermal time constant, 682  
   voltage responsivity, 652  
 PZT, 672, 681  
 Q-factor, 672  
 Quantization  
   of angular momentum, 241-245  
   of energy, 230, 236-241  
   space, 241-245, 247  
 Quantum leak. *See* Tunneling  
 Quantum numbers, 214, 232  
 magnetic, 232, 241, 270  
 orbital angular momentum, 232,  
   241-245, 270  
 principal, 232, 270  
 quantum state, 234  
 spin magnetic, 246, 271  
 Quantum physics, 191-283  
 harmonic oscillator, 337-342  
 tunneling, 221-228, 271, 278  
 Quartz oscillators and filter, 644-647  
 Quartz crystal  
   equivalent circuit, 646  
   inductance, 647  
 Quiescent point, 529  
 Radial function, 233-236  
 Radial probability density, 233  
 function, 236  
 Radiant, 260  
   flux, 269, 271, 853  
   power, 271  
 Radiant emission, 203. *See also* Black-  
   body radiation  
 Radiation, 271  
   brightness, 853-854  
 Radiative recombination center, 822  
 Radiometry, 853  
   flux in, 269, 853  
 Random motion, 416-422  
 Rare earth cobalt, magnets, 726  
 Rayleigh scattering, 816-817  
   in silica, 819  
 Rayleigh-Jeans law, 203  
 Recombination, 383, 407-409, 457-458,  
   463, 469  
   capture coefficient, direct, 469  
   current, 487-489, 572  
   direct, 407-409, 469  
   indirect, 407-409, 457-458  
   lifetime, 469  
   mean recombination time, 412, 487  
   and minority carrier injection, 407-416  
   rate, 469  
 Reflectance, 799-803, 807, 843  
   infrared, 811  
 Reflection of light, 793-799  
   coefficient, 793-799, 807, 843  
   external, 797, 801-802, 846  
   internal, 796, 797, 800-801, 846  
   at normal incidence, 796  
   phase changes, 795  
 Refracted light, 789-790, 843  
   phase changes, 795  
   transmission coefficients, 793-799,  
   844  
 Refractive index, 777-779, 844  
   complex, 804-811  
   definition, 777  
   dispersion relation, 773, 781-782,  
   842, 846  
   dispersion relation in diamond, 846  
   dispersion relation in GaAs, 783  
   field emission, 838  
   isotropic, 777  
   at low frequencies, 778  
   temperature coefficient, 845  
   versus wavelength, 779-784  
 Relative atomic mass. *See* Atomic mass  
 Relative permeability, 692, 762  
 Relative permittivity, 383, 584-585, 672,  
   673, 778, 781, 844

- complex, 605, 670, 804  
 definition, 584, 672  
 effective, 667  
 loss angle, 610  
 real and imaginary, 605-614  
 table, 602, 610
- Relaxation peak, 607  
 Relaxation process, 606  
 Relaxation time, 117, 179, 604, 672  
 Remanence. *See under* Magnetization  
 Remanent magnetization. *See under*  
 Magnetization
- Residual resistivity, 128, 179  
 Resistivity, effective, 140  
 Resistivity index (n), 132  
 Resistivity of metals (Table), 129  
 due to impurities, 138  
 graph, 130  
 Resistivity of mixtures and porous  
 materials, 139-144  
 Resistivity of thin films, 167-172  
 Resistivity-mixture rule, 140, 142  
 Resonant frequency. *See* Frequency,  
 resonant
- Reststrahlen absorption, 811-812  
 Reststrahlen band, 811  
 Retarding plates, 833-835, 844,  
 847  
 half-wave retarder, 834  
 quarter-wave retarder, 835  
 quartz retarder, 835  
 relative phase shift, 834  
 retardation, defined, 834
- Reverse bias, 489-493, 572. *See also*  
*pn junction*
- RF heating, 77  
 Rhombohedral crystal, 97  
 Richardson-Dushman equation, 328-332,  
 333  
 Root mean square velocity, 40  
 Rydberg constant, 245
- Saturated solution, 102  
 Saturation of magnetism, 703-704  
 Schottky defect, 66, 102  
 Schottky effect, 332-337  
 Schottky coefficient, 333  
 Schottky junction, 435-443, 464  
 built in electric field, 437  
 built in potential, 437  
 depletion region, 437  
 diode, 435-440  
 energy band diagram, 436, 438,  
 440  
 I-V characteristic, 438  
 Schottky barrier height, 437  
 Schottky junction equation, 440  
 solar cell, 440-443  
 space charge layer (SCL), 437  
 Schrödinger's equation, 208-212, 271,  
 450  
 for three dimension, 209  
 time dependent, 208-209  
 time independent, 208-212, 271  
 SCL. *See* Space charge layer  
 Screw dislocation, 69, 102  
 line, 69
- Secondary bonding, 18-22, 102  
 Secondary emission, 368-369  
 Seebeck effect, 322-328, 364-365  
 in semiconductors, 472-473  
 Mott and Jones equation, 324  
 Seebeck coefficient, 322-323
- Seed, 77  
 Selection rules, 242-243, 271  
 Sellmeier coefficients, 782  
 Sellmeier equation, 782, 845  
 Semiconductor bonding, 299-302
- Semiconductor devices, 475-581  
 ultimate limits to device performance,  
 578
- Semiconductor optical amplifiers,  
 566-569  
 active layer, 567  
 optical amplification, 568
- Semiconductors, 299-303, 373-473  
 conduction band (CB), 302  
 degenerate and non-degenerate,  
 406-407  
 direct and indirect bandgap, 448-458,  
 814-815  
 strain gauge, 434-435  
 tables, 366, 386  
 valence band (VB), 301
- Series rule of mixtures, 140  
 Shell model, 3
- Shackley, William, 372, 473  
 Shackley equation, 485, 572  
 Short-range order, 79
- Silicon, 80, 299-301, 374-380  
 amorphous, 80-82, 459. *See also* a-Si:H  
 conduction band, 302  
 crystalline, 80-82  
 energy band diagram, 374  
 hybrid orbitals, 300  
 hydrogenated amorphous silicon  
 (a-Si:H), 82, 459  
 properties (table), 674  
 valence band, 301  
 zone refining, 88-90
- Silicon gate technology. *See* Polysilicon  
 gate
- Silicon single crystal growth, 76-77  
 Skin depth for conduction, 163  
 Skin effect in inductor, 166  
 Skin effect: HF resistance of conductor,  
 163-166, 179  
 at 60 Hz, 188
- Small signal equivalent circuit, 572  
 Snell's law, 790-792, 844
- Soft magnetic materials, 721-724, 763  
 table, 722
- Solar cell, 475, 551-563, 581  
 antireflection coating, 551, 802-803,  
 841, 846  
 fill factor, 558, 571  
 finger electrodes, 551  
 I-V characteristics, 556-557  
 load line, 557  
 materials, devices and efficiencies,  
 561-563  
 maximum power delivered, 580  
 normalized current and voltage, 580  
 open circuit voltage, 552, 558-559  
 operating point, 557  
 passivated emitter rear locally diffused  
 cells (PERL), 561-562  
 photocurrent, 553, 572  
 photovoltaic device principles, 551-559  
 power delivered to the load, 557  
 Schottky junction, 440-443  
 series resistance, 559-561, 581  
 short circuit current, 556  
 shunt (parallel) resistance, 559-561,  
 581  
 total current, 556
- Solder (Pb-Sn), 90-95, 111  
 Solid solution and Northcote's rule,  
 134-139, 182  
 Co-Au, 137  
 Co-Ni, 135
- Solid solutions, 65, 83-95, 102, 179  
 interstitial, 84  
 intermetallic, 83  
 substitutional, 65
- Solidification, nucleation, 70
- Solids curve, 85  
 Solute, 83, 102  
 Solvent, 83, 102  
 Solvus curve, 90  
 Sound velocity, 347  
 Space charge layer (SCL), 437, 477. *See*  
*also pn junction*
- Specific heat capacity, 31, 101  
 Spectral irradiance, 202  
 Spherical harmonic, 232  
 Spin, 245-247  
 of an electron (defined), 271  
 magnetic moment, 280  
 magnetic quantum number, 246  
 paired, 255  
 Stern-Gerlach experiment, 250  
 Spin-orbit coupling, 280-281  
 potential energy, 281  
 Spontaneous emission, 259, 271  
 Sputtering, 167  
 SQUID, 731
- State, electronic, 234, 247, 271, 365  
 ground, 215  
 stationary state, 210
- Statistics, 312-315  
 Boltzmann classical statistics, 312-313,  
 363  
 Boltzmann tail, 315  
 Fermi-Dirac statistics, 123, 312-315, 364  
 of donor occupation, 390, 465  
 of dopant ionization, 400  
 Stefan-Boltzmann law. *See* Blackbody  
 radiation
- Stefan's black body radiation law, 179,  
 203-204  
 Stefan's constant, 203-204  
 Stimulated emission, 259, 271  
 Stoichiometric compounds, 75, 102  
 Stoichiometry, 75-76  
 Stok's shaft, 822, 844  
 Strain, 24, 102  
 shear strain, 102  
 volume strain, 102  
 Strain gauge, 186  
 Stress, 24, 102  
 shear stress, 102
- Strong force, 4  
 Substrate, 544, 572
- Superconducting solenoid, 737-739, 771  
 Superconductivity, 685, 729-740, 763  
 critical current, 736-739, 769  
 critical magnetic field, 735, 760  
 critical surface, 737  
 critical temperature, 729, 760  
 high  $T_c$  materials, 731, 736  
 Meissner effect, 729-733, 762  
 Meissner state, 734  
 origin, 739-740  
 penetration depth, 734  
 table, 736  
 type I and II, 733-736, 763  
 vortex state, 735  
 weak link, 757  
 zero resistance, 729-733
- Supercooled liquid, 78  
 Surface current, 690  
 Surface polarization charges, 589  
 density, 590  
 Surface scattering, 168  
 Surface tracking, 628, 672. *See also*  
 Dielectric breakdown
- Temperature coefficient of capacitance  
 (TCC), 672, 677  
 Temperature coefficient of resistivity  
 (TCR  $\alpha$ ), 125-134, 180, 182  
 definition, 128  
 metals (table), 129

- Temperature dependence of resistivity in  
 pure metals, 122-125
- Temperature of light bulb filament, 187
- Ternary alloys, 345
- Terrace-ledge-kink model. *See* Kossel  
 model
- Tetragonal crystals, 97
- Thermal coefficient of linear expansion,  
 33, 102, 187
- Thermal conduction, 149-154, 185
- Thermal conductivity, 149-153, 180  
 Ag, 183  
 due to phonons, 348  
 graph (versus electrical conductivity),  
 150  
 of nonmetals, 348-350  
 table, 152
- Thermal equilibrium, 40
- Thermal equilibrium carrier concentration,  
 397, 464
- Thermal evaporation, 167
- Thermal expansion, 31-36, 102
- Thermal expansion coefficient. *See*  
 Thermal coefficient of linear  
 expansion
- Thermal fluctuations, 40-45
- Thermal generation, 376
- Thermal generation current, 572-573
- Thermal radiation, 202. *See also* Blackbody  
 radiation
- Thermal resistance, 153-154, 180, 185
- Thermal velocity, 40, 387, 401, 464
- Thermalization, 427
- Thermally activated conductivity, 161, 179
- Thermally activated processes, 45-49, 161  
 activated state and activation energy,  
 46, 161
- Arrhenius type behavior, 45
- diffusion, 46
- diffusion coefficient, 48
- jump frequency, 47
- root mean square displacement, 48
- Thermionic emission, 328-332, 365, 369  
 constant, 331
- Thermocouple, 322-328  
 equation, 325, 327-328, 369
- Thermoelectric cooler, 443-448
- Thermoelectric emf, 325, 327  
 metals (table), 326
- Thermoelectric power, 322-323
- Thin film, 180, 188
- Thin film head, 752
- Thin metal films, 166-172
- Threshold voltage, 539-541, 573
- Toroid, 693-696, 765
- Total internal reflection (TIR), 789-792,  
 797, 844  
 critical angle, 791, 842  
 phase change in, 797
- Transducer. *See* Piezoelectric, transducer
- Transistor action, defined, 509, 573. *See  
 also* Bipolar junction transistor
- Transition temperature, 61
- Transmission coefficient, 844
- Transmittance, 799-803, 844
- Transverse electric field, 793
- Transverse magnetic field, 793
- Trapping, 409
- Triclinic crystal system, 97
- Tunneling, 221-228, 271, 278  
 field-assisted probability, 334  
 probability, 223  
 reflection coefficient, 223  
 scanning tunneling microscope,  
 223-227  
 transmission coefficient, 222-223
- Two-phase alloy resistivity, 143-144  
 Ag-Ni, 143
- Two phase solids, 83-95
- Unharmonic effect, 34
- Unharmonic oscillations, 34
- Unharmonicity, 34, 349
- Uniaxial crystals, 828
- Unipolar conductivity, 118
- Unit cell, 50, 56, 97, 102  
 hexagonal, 52
- Unpolarized light, 796
- Upper cut-off (threshold) wavelength, 813  
 graph, 814  
 table, 813
- Vacancy, 64-68, 102, 110  
 concentration in Al, 67  
 concentration in semiconductor, 67-68
- Vacuum deposition, 106-107
- Vacuum level (energy), 292-295, 464
- Vacuum tubes, 328-337  
 rectifier, 329  
 saturation current, 329
- Valence band (VB), 301, 374-378, 464
- Valence electrons, 5, 102
- Valency of an atom, 5
- van der Waals bond, 19-20  
 water (H<sub>2</sub>O), 20
- van der Waals-London force, 19
- Vapor deposition, 167. *See also* Physical  
 vapor deposition
- Varactor diodes, 499
- Verhulst equation, 467
- VB. *See* Valence band
- Velocity density (distribution) function, 37
- Vibrational wave, 151
- Viral theorem, 6, 7, 102-103
- Vitreous silica, 78
- Volume expansion, 35
- Volume expansion coefficient, 35
- Voigt's state, 735
- Wave, defined, 271-272  
 dispersion relation, 364, 666, 842  
 electromagnetic (EM), 191  
 energy densities in an EM, 787  
 equation, 272, 347
- fields in EM, 787  
 group velocity, 341  
 incident, 793  
 lattice, 340  
 light waves, 774-776  
 longitudinal, 339  
 matter waves, 210  
 monochromatic plane EM, 774  
 phase, 774, 843  
 phase velocity, 776, 777, 843  
 propagation constant, 774  
 reflected, 793  
 transmitted, 793  
 transverse, 339  
 traveling, 192, 774-775  
 ultrasonic, 641  
 vibrational, 151
- Wavefront, 774, 844
- Wavefunction, 208-210  
 antisymmetric, 216  
 defined, 272  
 eigenfunction, 210  
 matter waves, 210  
 one-electron, 254  
 stationary states, 210  
 steady state total, 209  
 symmetric, 216
- Wave number, 192, 774, 844. *See also*  
 Wavevector
- Wavepacket, 784, 844
- Wavevector (k), defined, 192, 272, 776, 844  
 of electron, 272, 450-456
- Weak injection, 425
- Weight fractions, 8-9, 88
- White LED, 820-825
- Wiedemann-Franz-Lorenz's law, 150
- Wien's displacement law, 205, 277
- Weak function, 196, 272, 295, 365,  
 435-437, 463, 464  
 effective, 333  
 of a semiconductor, 384  
 table, 295, 360, 470
- X rays, 193-194, 199-202, 272, 275-276,  
 367, 848  
 diffraction, 849-852  
 energy fluence, 275  
 photon fluence, 276  
 radiography, 275  
 roentgen, 275
- Young's double-slit experiments (figure),  
 193, 205
- Young's fringes, 192
- Young's modulus, 102. *See also* Elastic  
 modulus
- Zener breakdown, 502-506, 573
- Zener effect, 505
- Zener resistance, 729-733
- Zeno-point energy, 365
- Zinc refining, 88-90

"We have a habit in writing articles published in scientific journals to make the work as finished as possible, to cover up all the tracks, to not worry about the blind alleys or describe how you had the wrong idea first, and so on. So there isn't any place to publish, in a dignified manner, what you actually did in order to get to do the work."

Richard P. Feynman  
 Nobel Lecture, 1966